



Intrinsically low thermal conductivity in some Cu-based ternary / quaternary sulfides

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EPSRC Workshop - Manchester

Properties - Performances

Figure of Merit - zT

$$zT = \frac{\alpha^2 T}{\rho \kappa} \Rightarrow z = \frac{\alpha^2}{\rho \kappa}$$

α - Seebeck Coefficient

$$\alpha = \frac{8\pi^2 k_B^2}{3eh^2} m^* T \left(\frac{\pi}{3n} \right)^{2/3}$$

ρ - Electrical Resistivity

$$\rho = n e \mu$$

κ - Thermal Conductivity

$$\kappa = \kappa_e + \kappa_l$$

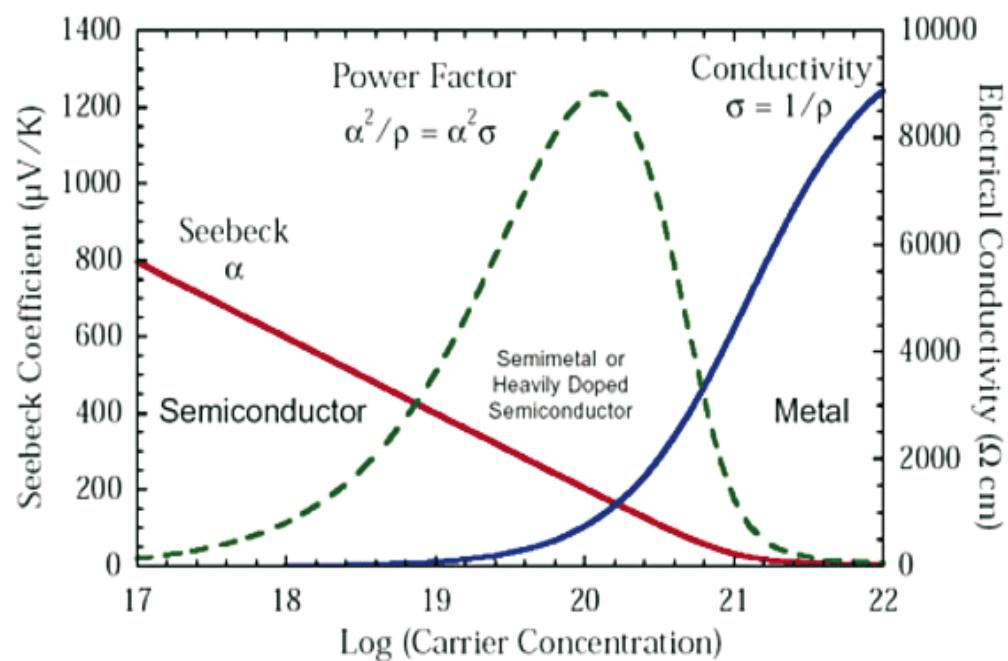
$$\kappa_e = L \sigma T = n e \mu L T$$

n - carrier concentration

m^* - effective mass of carrier

μ - carrier mobility

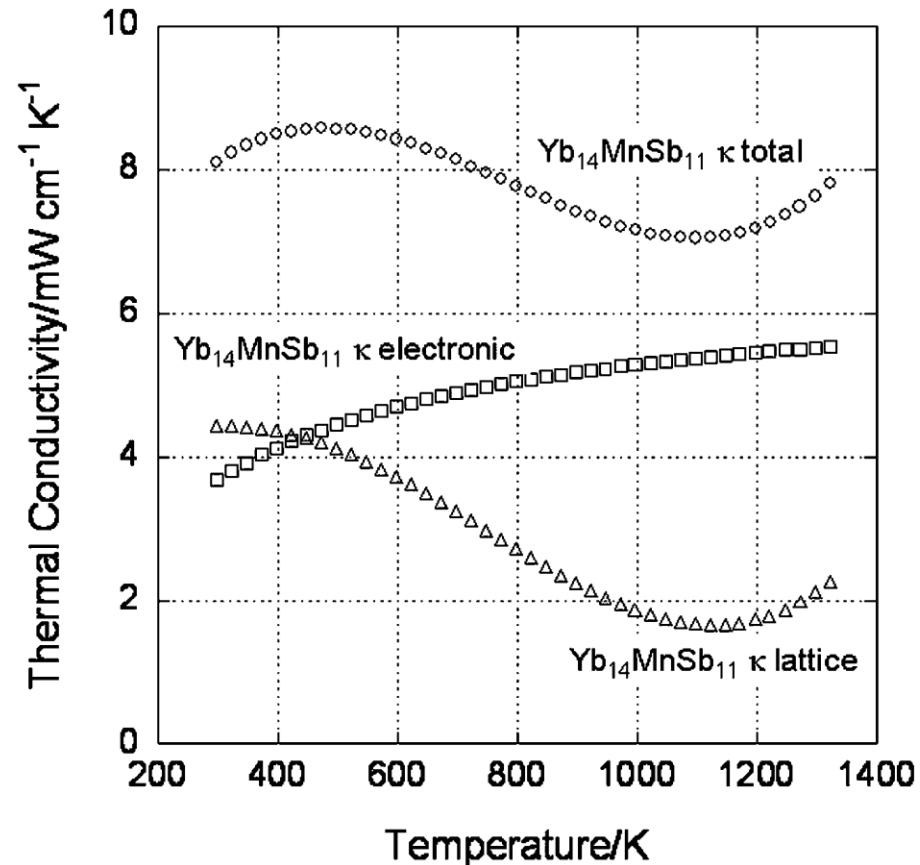
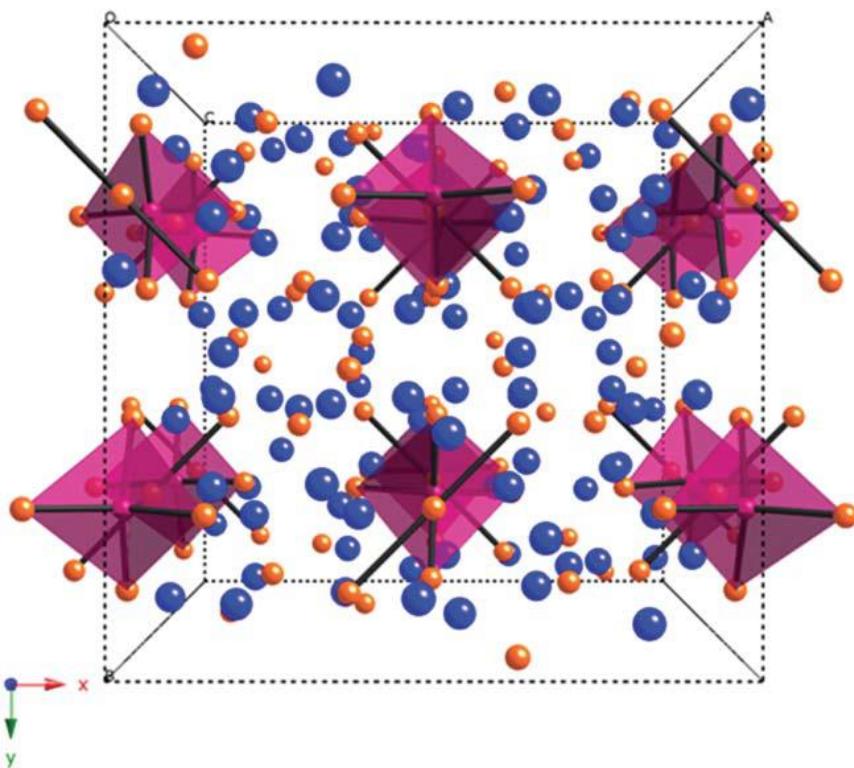
Optimized Carrier Concentration



Stopping/Scattering Phonons

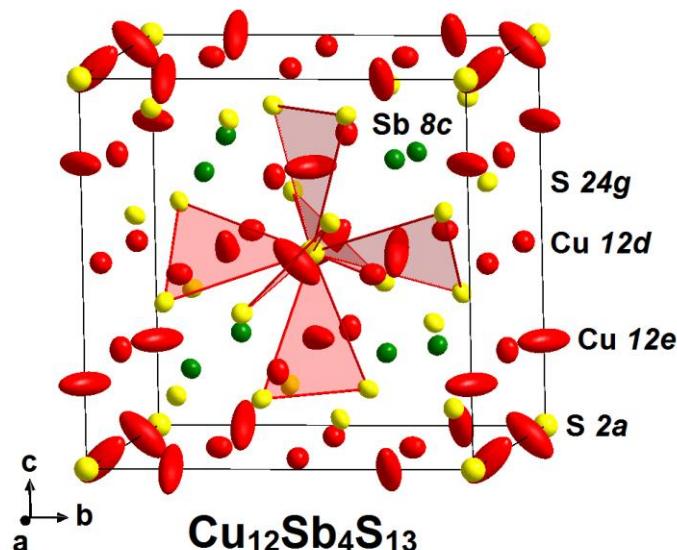


Complex Structures



S. R. Brown et al., $\text{Yb}_{14}\text{MnSb}_{11}$. New high efficiency thermoelectric material for power generation, Chem. Mater., 2006, 18, 1873–1877.

$\text{Cu}_{12}\text{Sb}_4\text{S}_{13}$: A complex structure with low K



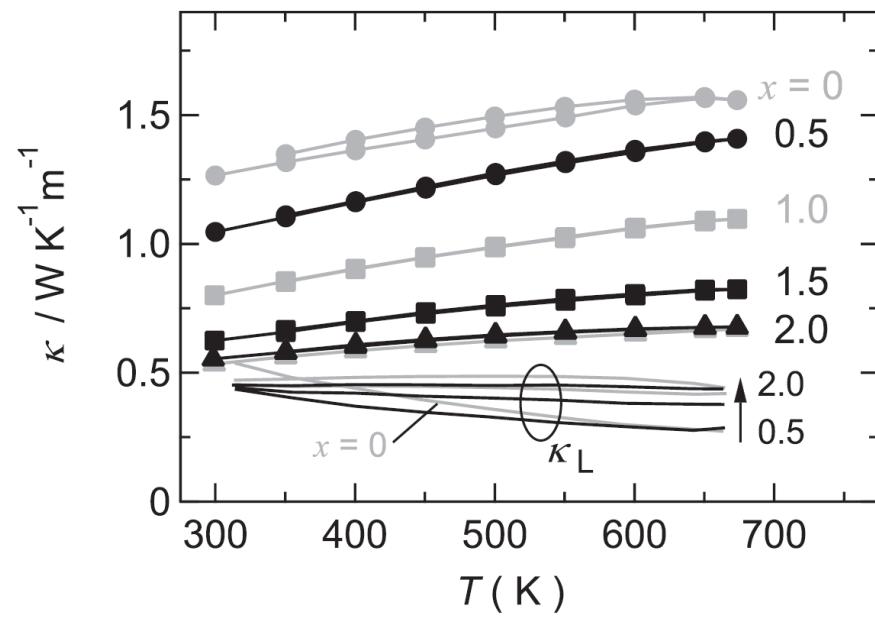
I-43m

$a \approx 10.3 \text{ \AA}$

Synthetic tetrahedrites evidence high $\angle I$ values:

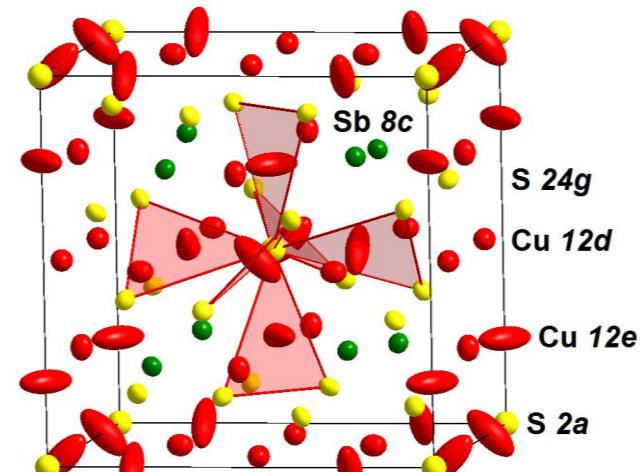
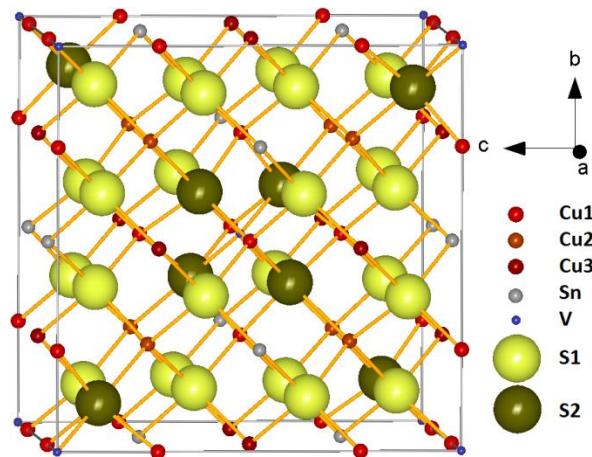
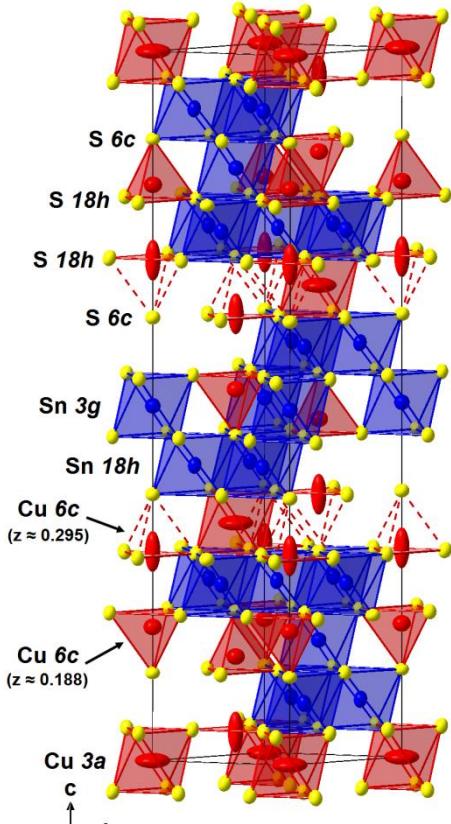
- **0.56** at 673 K for $\text{Cu}_{12}\text{Sb}_4\text{S}_{13}$ [1]
- **0.7** at 673 K for $\text{Cu}_{10.5}\text{Zn}_{1.5}\text{Sb}_4\text{S}_{13}$ [1]
- **0.7** at 665 K for $\text{Cu}_{10.5}\text{Ni}_{1.5}\text{Sb}_4\text{S}_{13}$ [2]

- Large number of elements
- Anharmonic Rattling
- Mass fluctuations

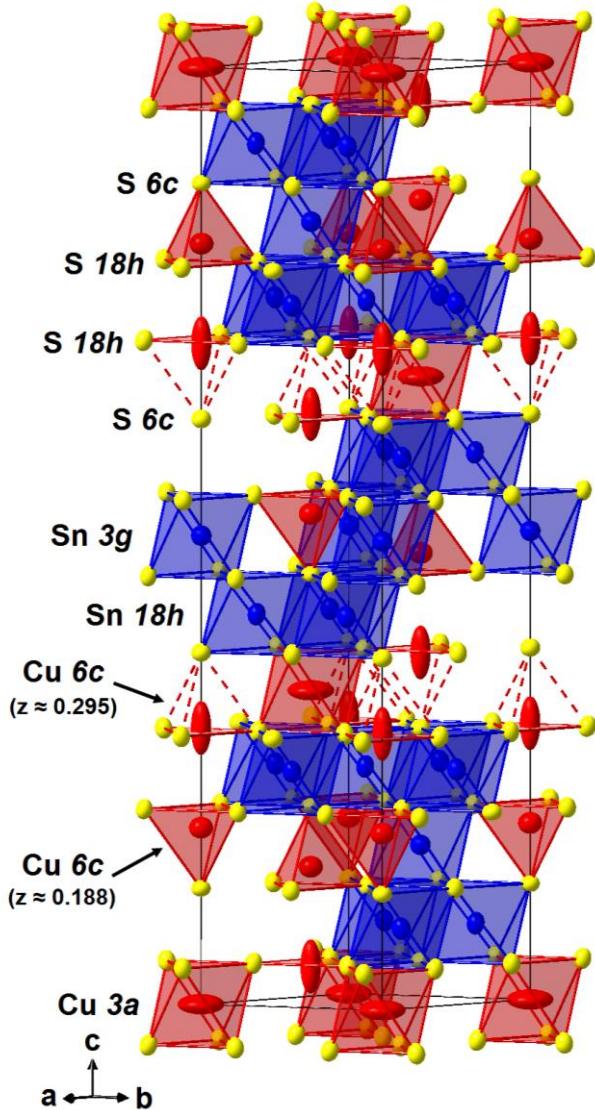


[1] X. Lu et al., Adv. Energy Mater. 3 (2013) 342-348. [2] K. Suekuni et al., J. Appl. Phys. 113 (2013) 043712.

Outline

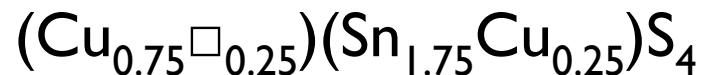


$\text{Cu}_4\text{Sn}_7\text{S}_{16}$



[I]
Rhombohedral symmetry
Space group R-3m ($n^\circ 166$)
 $a = 7.372 \text{ \AA}$ and $c = 36.010 \text{ \AA}$

- Defect variant of the AB_2X_4 spinel structure
Tetrahedral sites \rightarrow 2 non equivalent sites
Octahedral sites \rightarrow 3 non equivalent sites

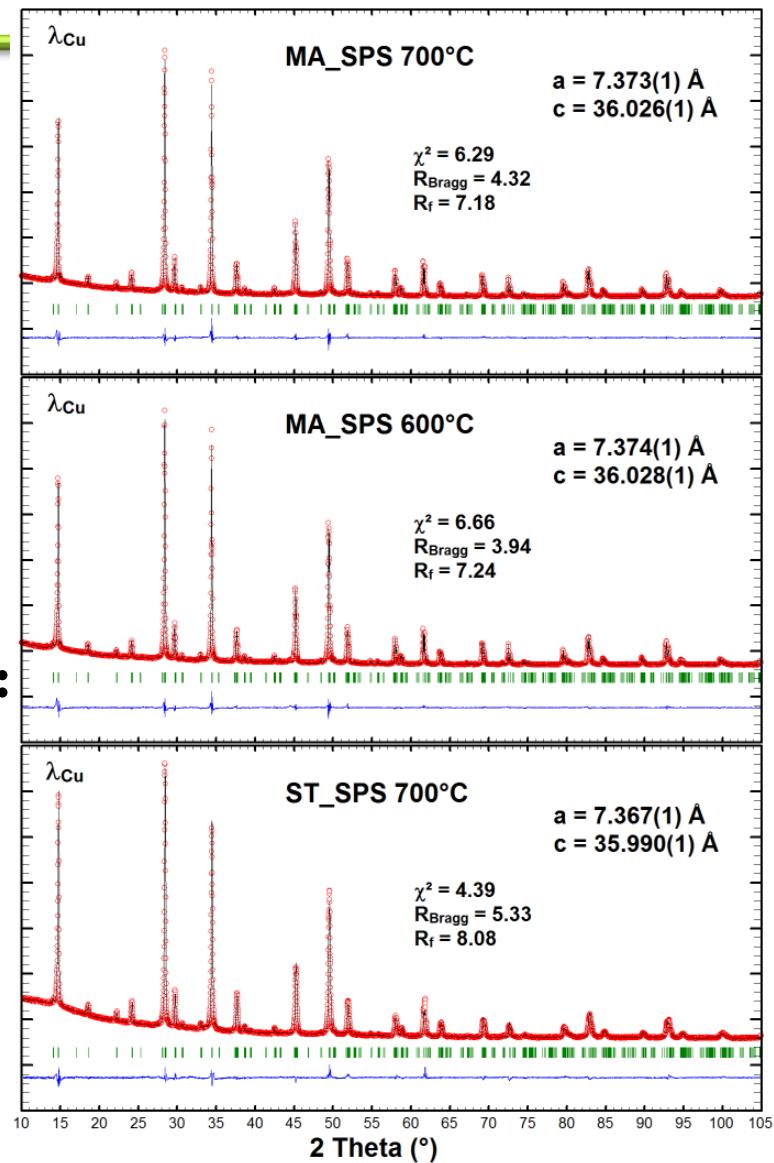


$\text{Cu}_4\text{Sn}_7\text{S}_{16}$

- Powder Synthesis
 - Sealed tube Synthesis (ST)
 - Mechanical Alloying (MA)
- SPS Sintering (600-700°C/50 MPa)

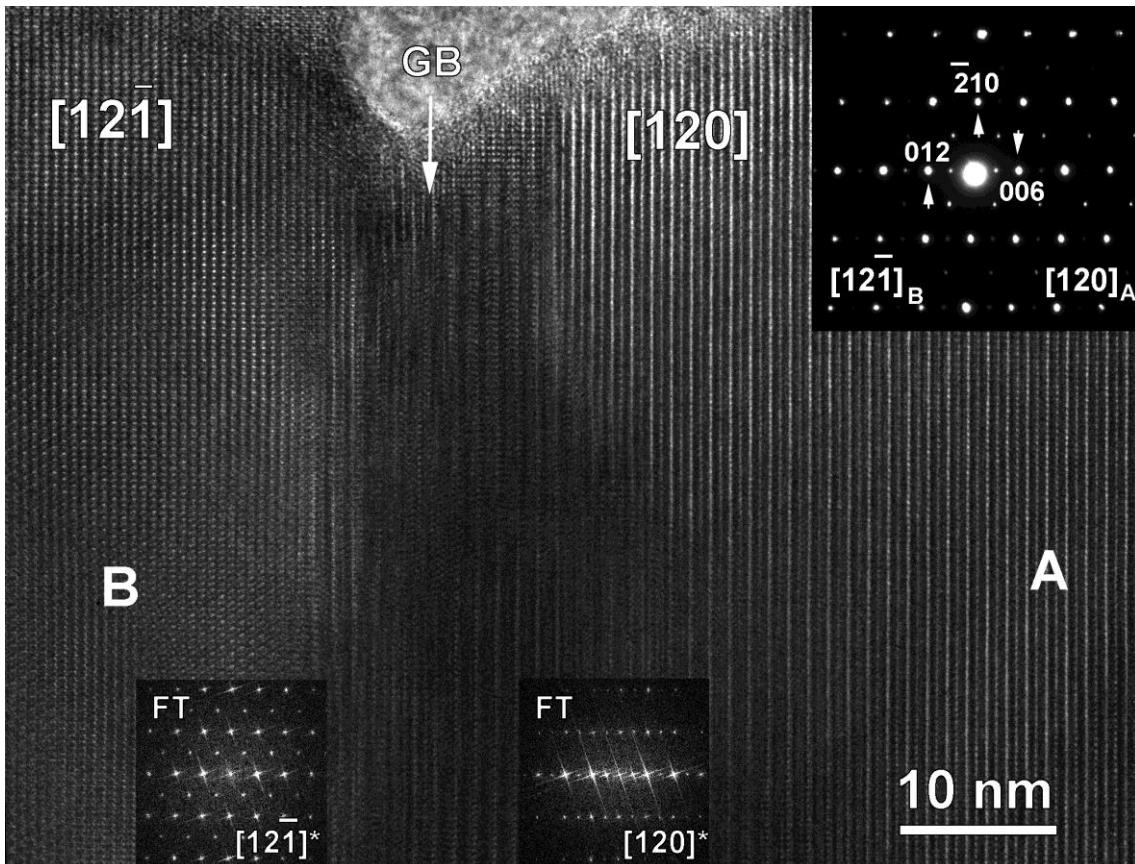
Similar structural parameters, except:

- Cell parameters (ST) < (MA)
(wide non-stoichiometry range)
- Lower crystallinity in ST samples
 - Composition inhomogeneity
 - Structural defects

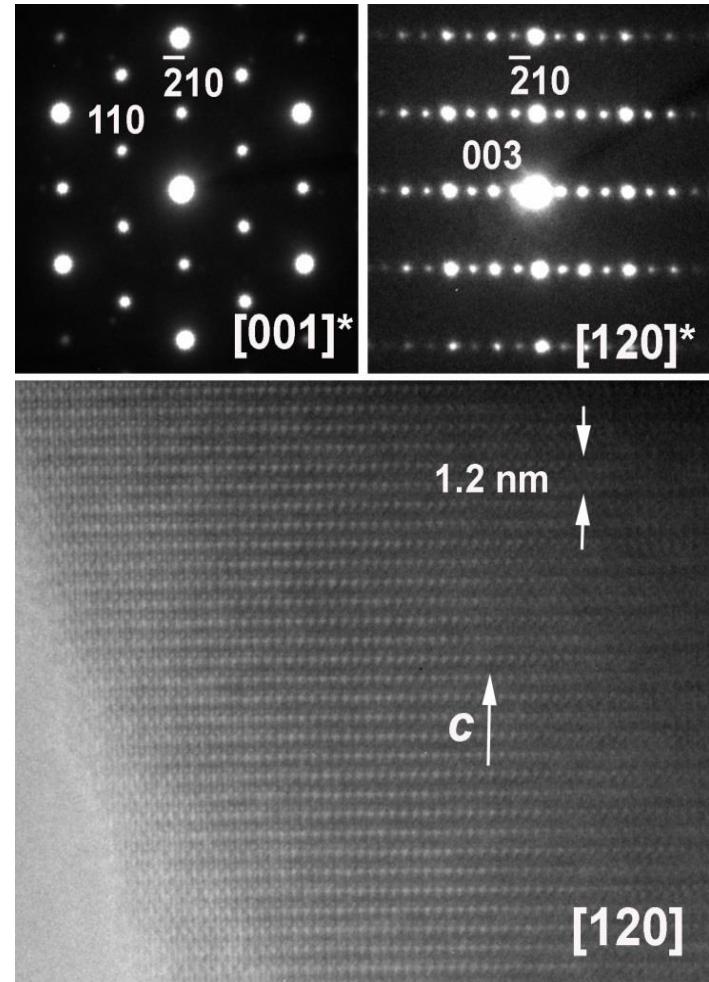


$\text{Cu}_4\text{Sn}_7\text{S}_{16}$

(ST)



(MA)

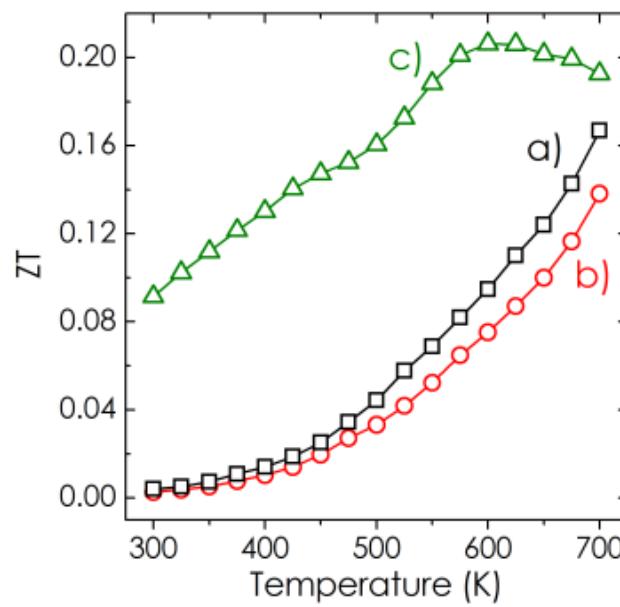
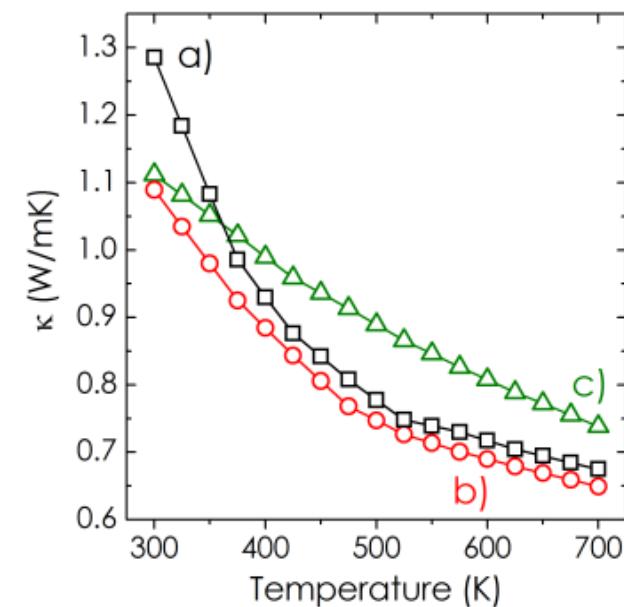
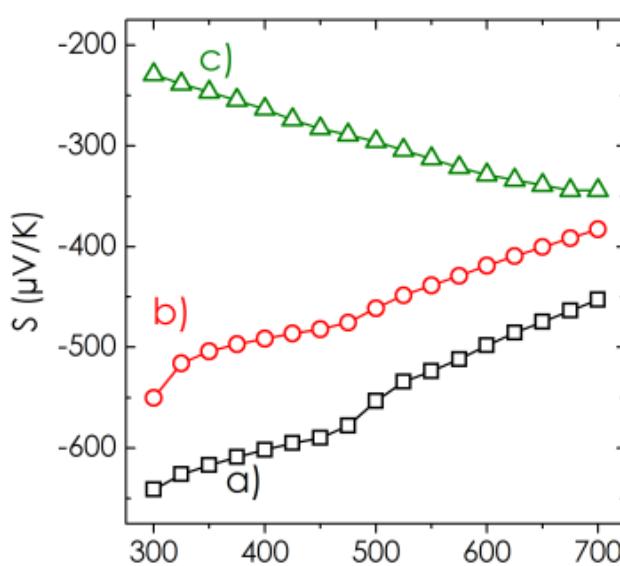
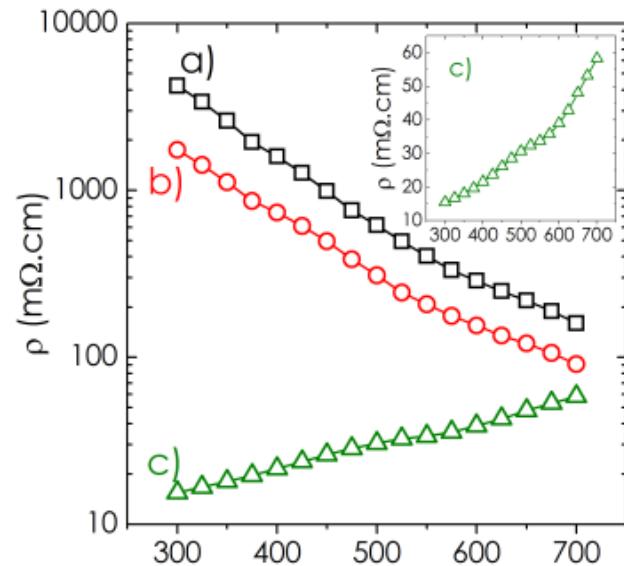


-Anisotropic crystallites

-Grain Boundaries: Twinning, Intergrowths

[120]

$\text{Cu}_4\text{Sn}_7\text{S}_{16}$



Mechanical alloying

a) 700°C and b) 600°C

Sealed tubes

c) 700°C

-Metallic behavior in ST

Sulfur vacancies

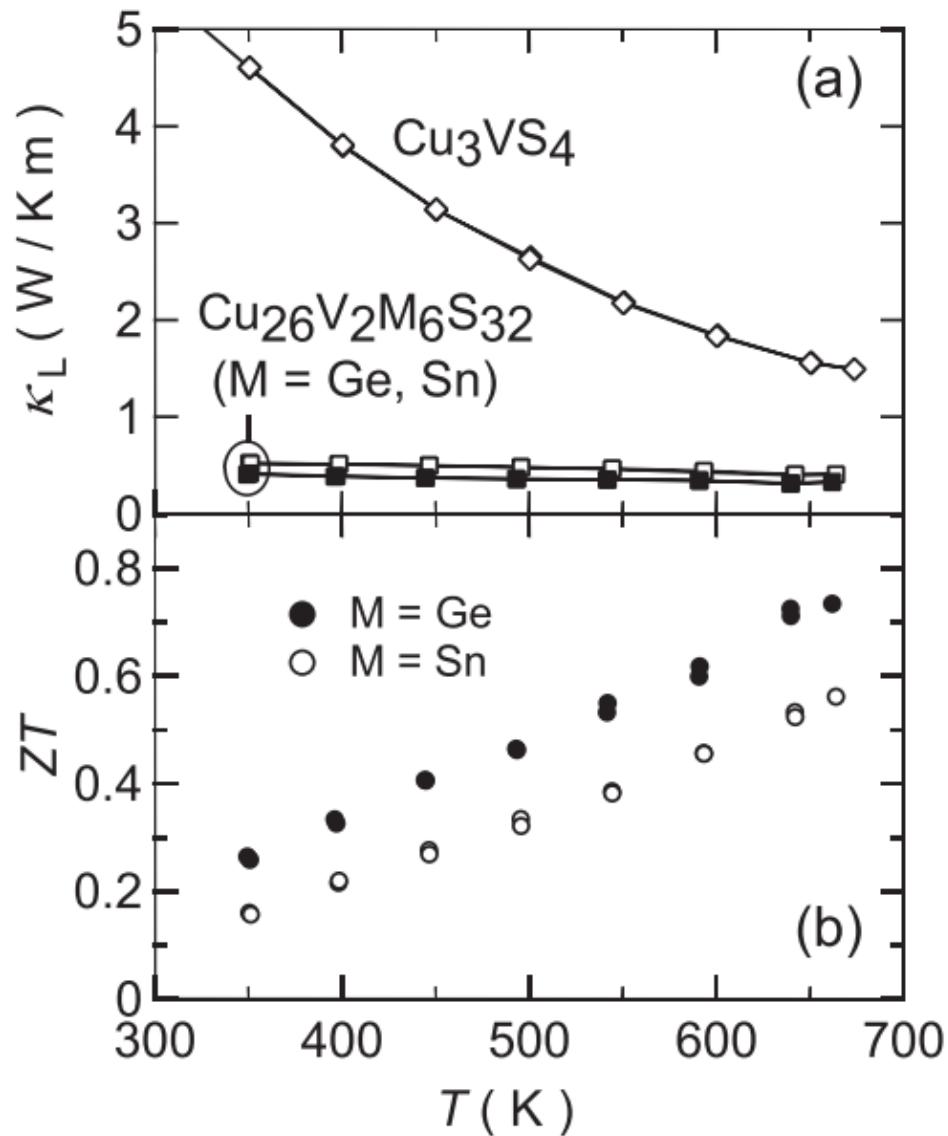
Vacancy occupation

-Low thermal conductivity

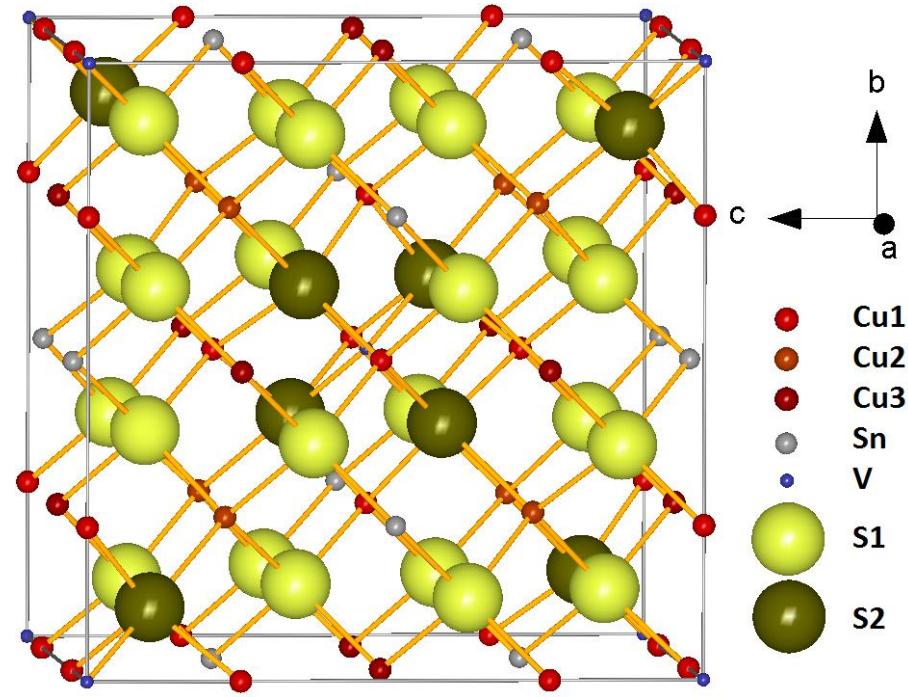
-ZT=0.2 @600K

Colusite : $\text{Cu}_{26}\text{V}_2\text{Sn}_6\text{S}_{32}$

Suekuni et al. APL 2014

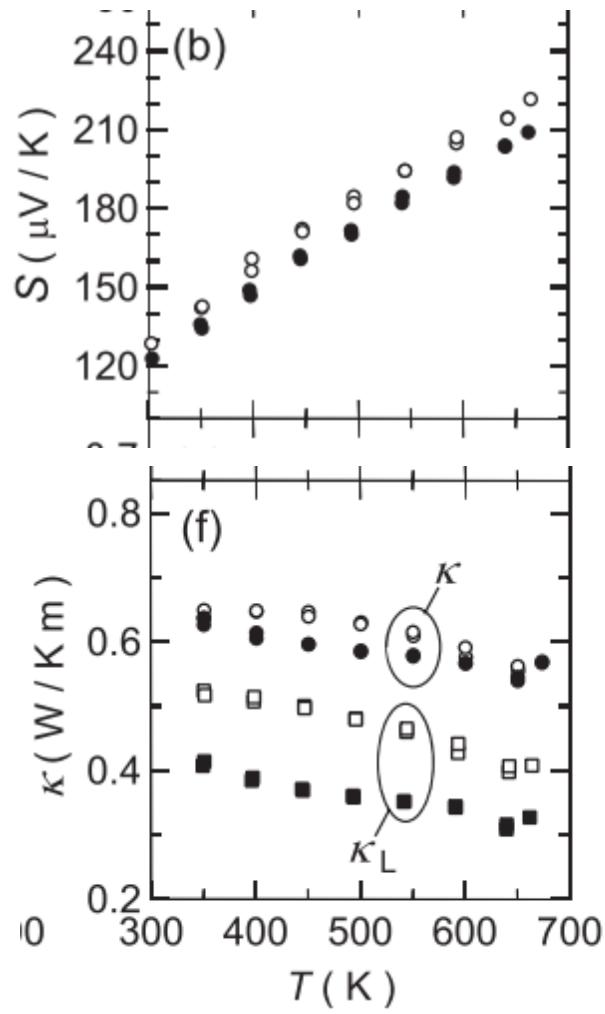


Cubic symmetry
Space group P-4 3 n (n°218)
 $a \approx 10.7 \text{ \AA}$
66 atoms per unit cell

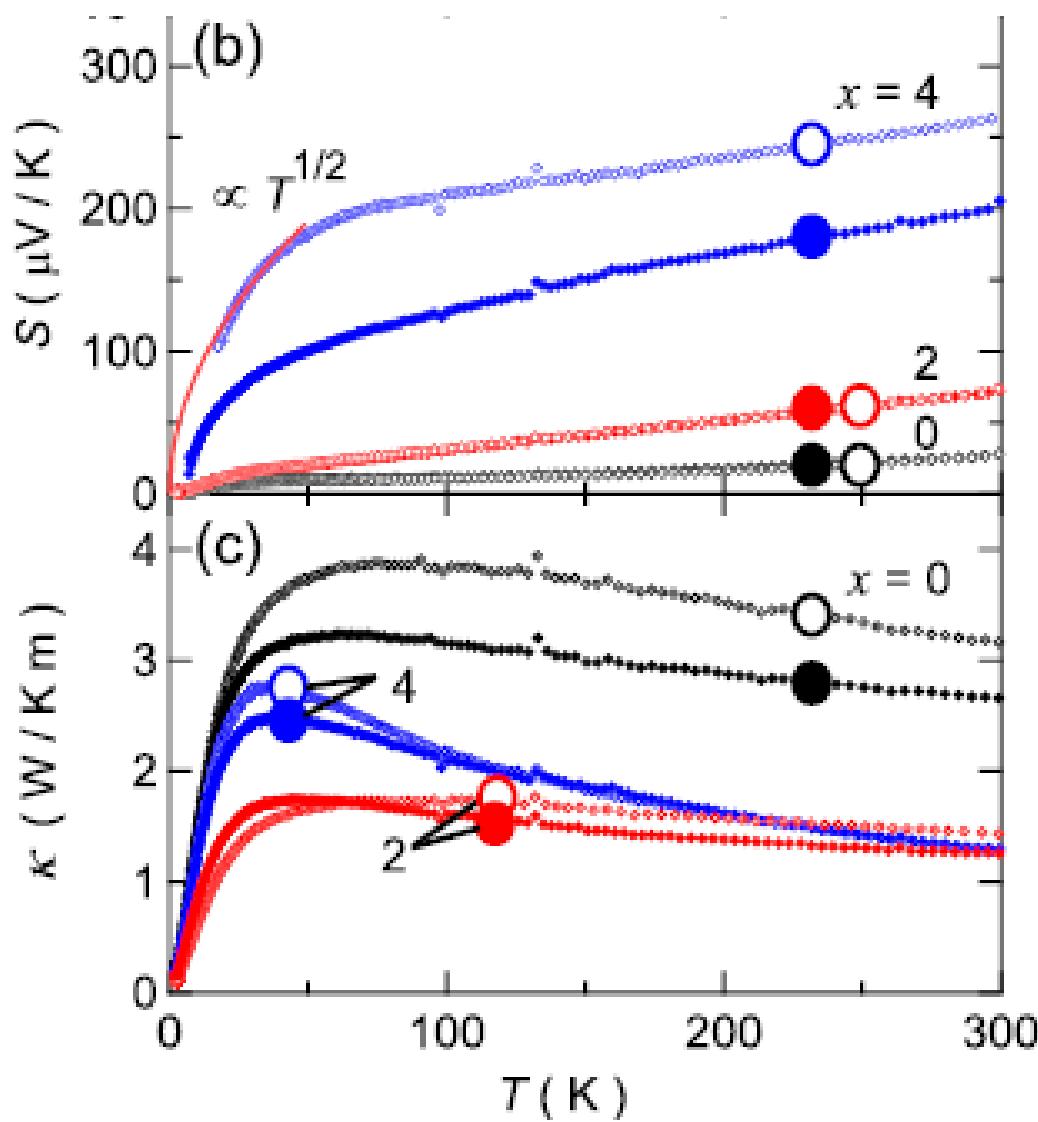


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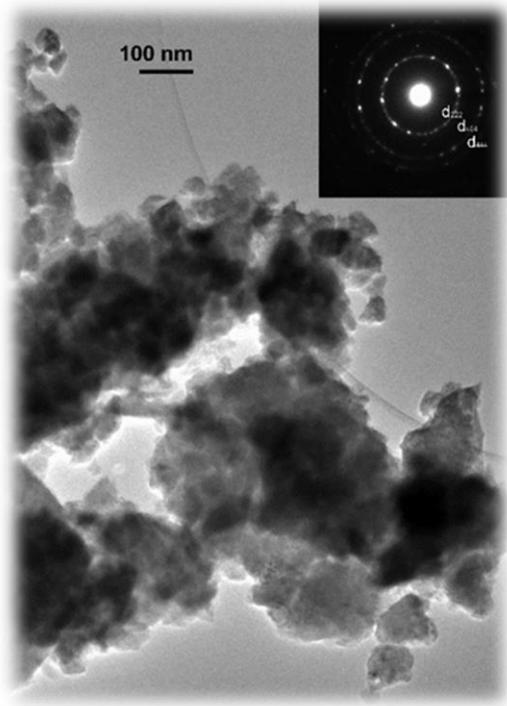
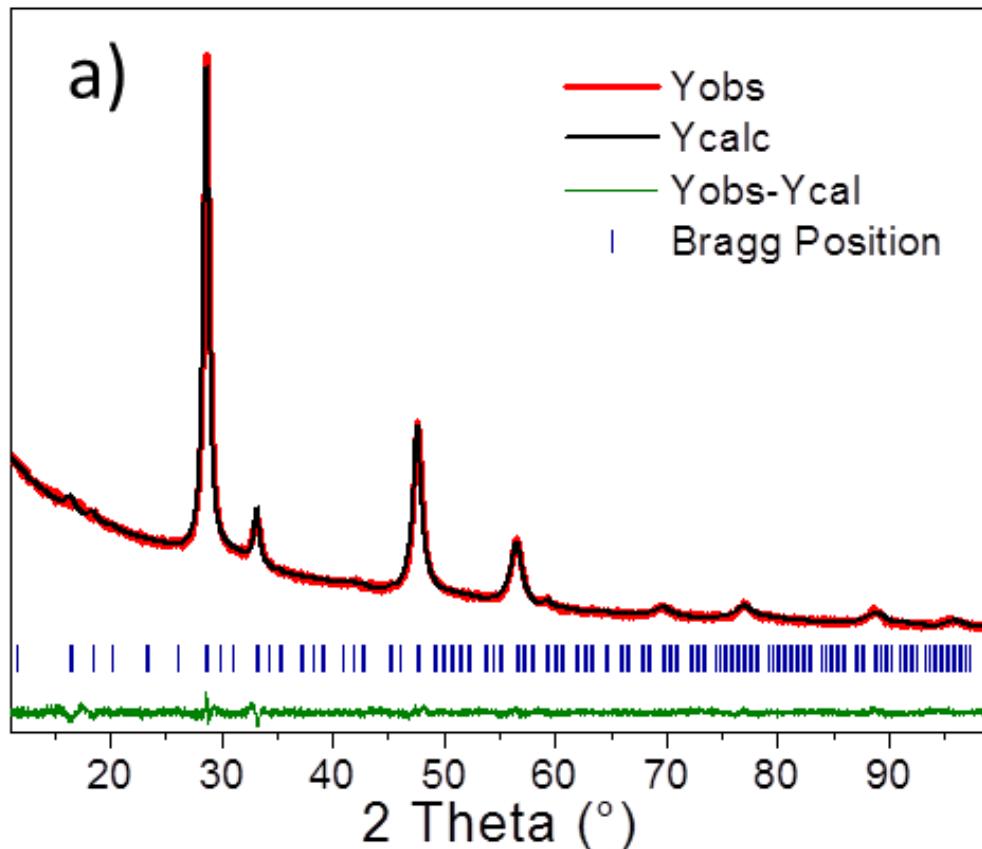


Suekuni et al. JAP 2014

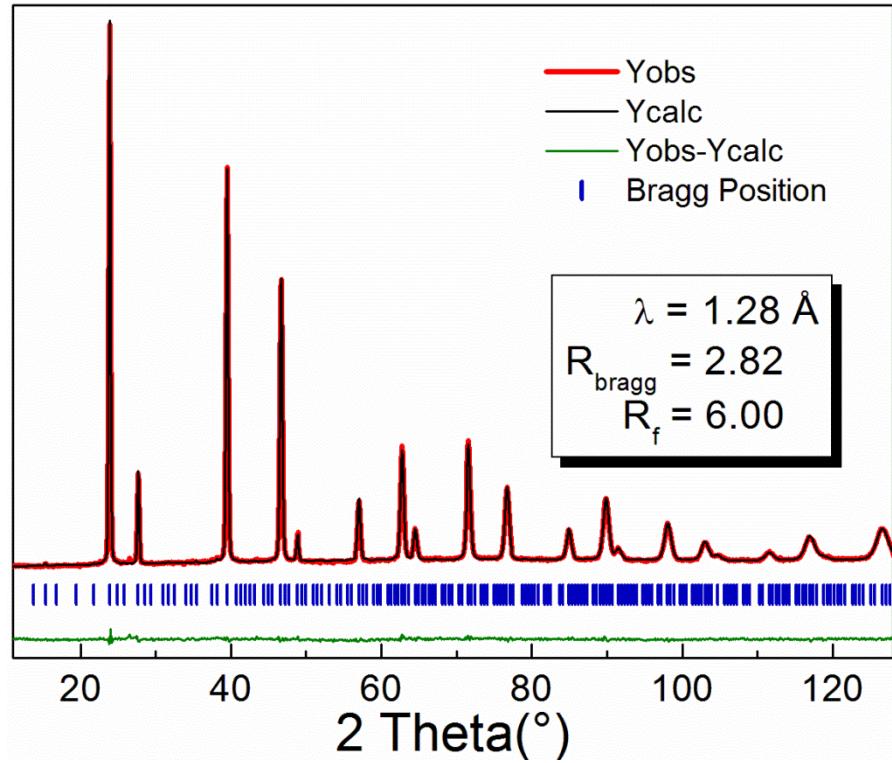
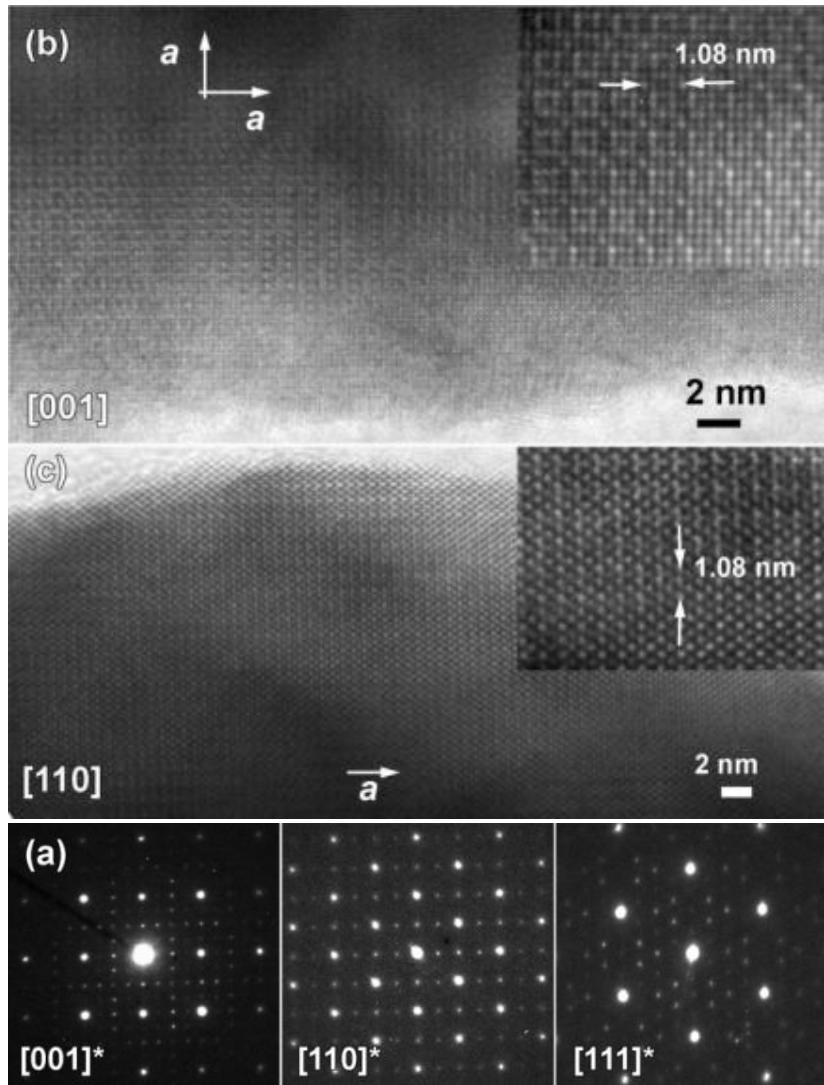


Mechanical Alloying

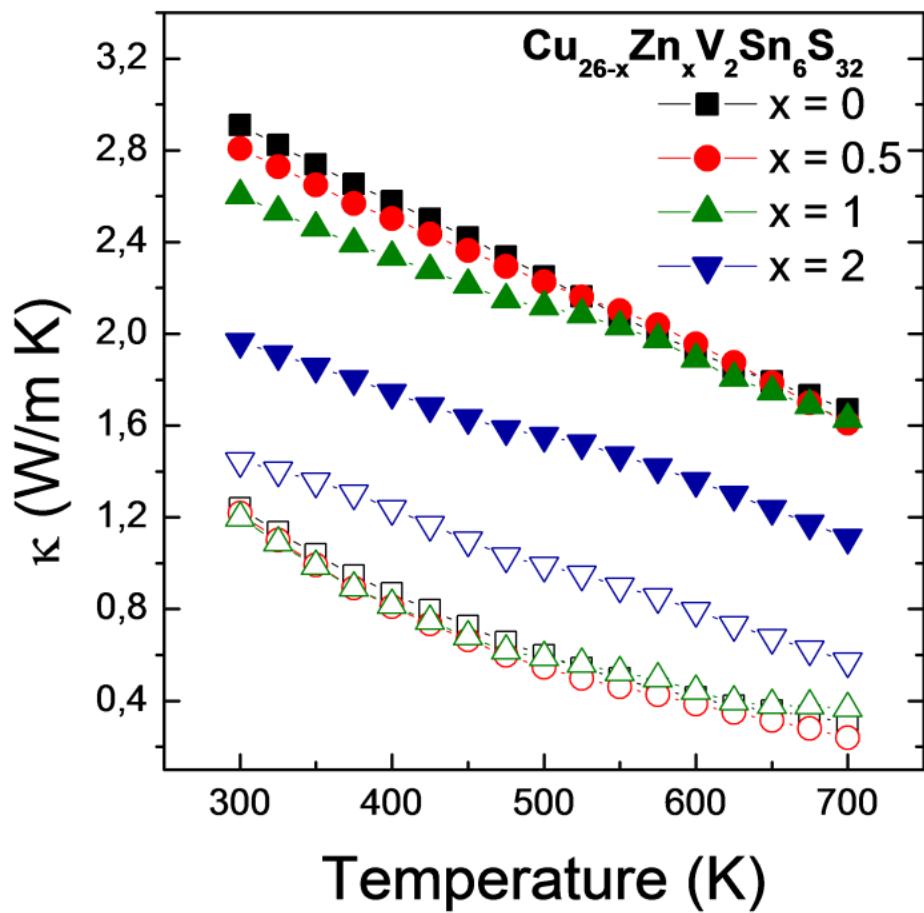
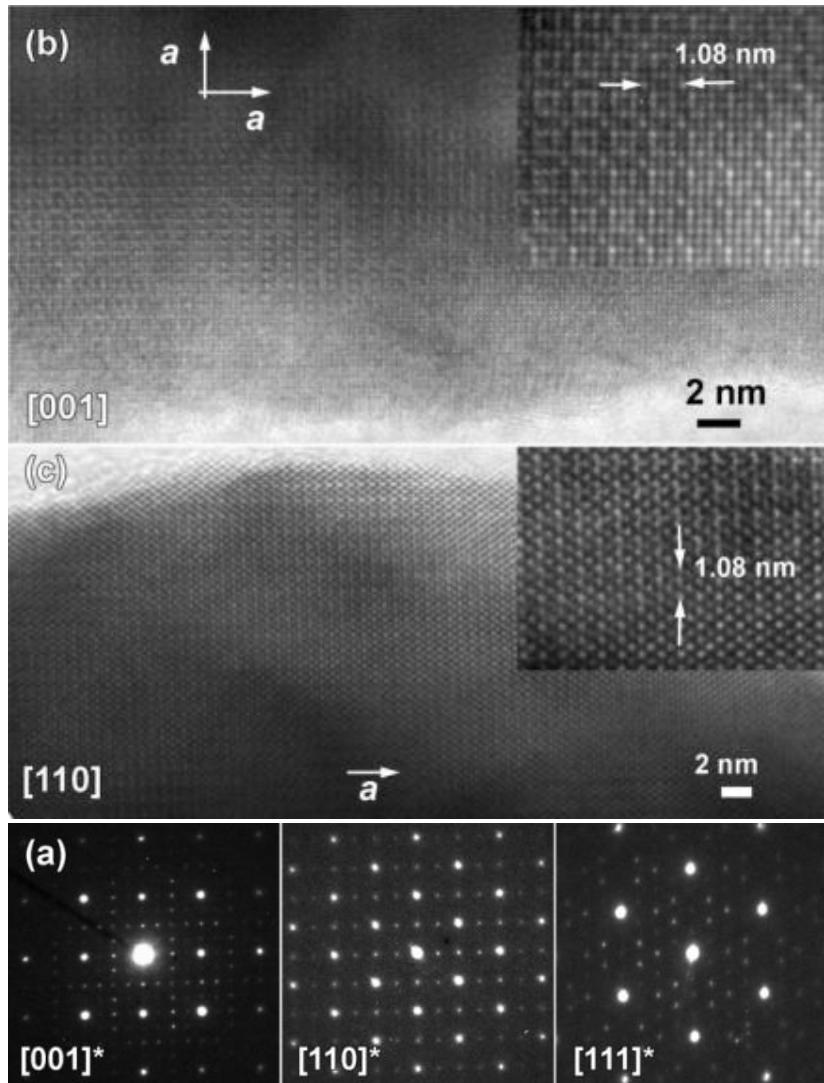
Homogeneity & reproducibility



Bulk Cu_{26-x}Zn_xV₂Sn₆S₃₂

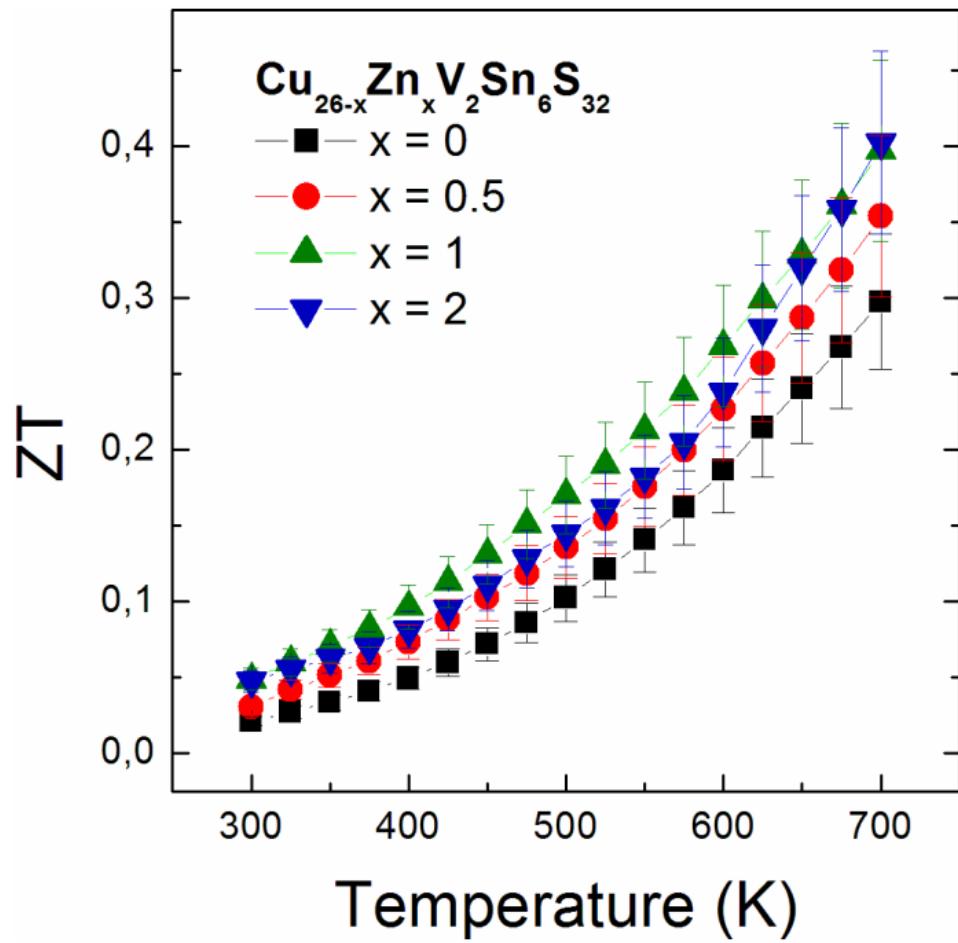
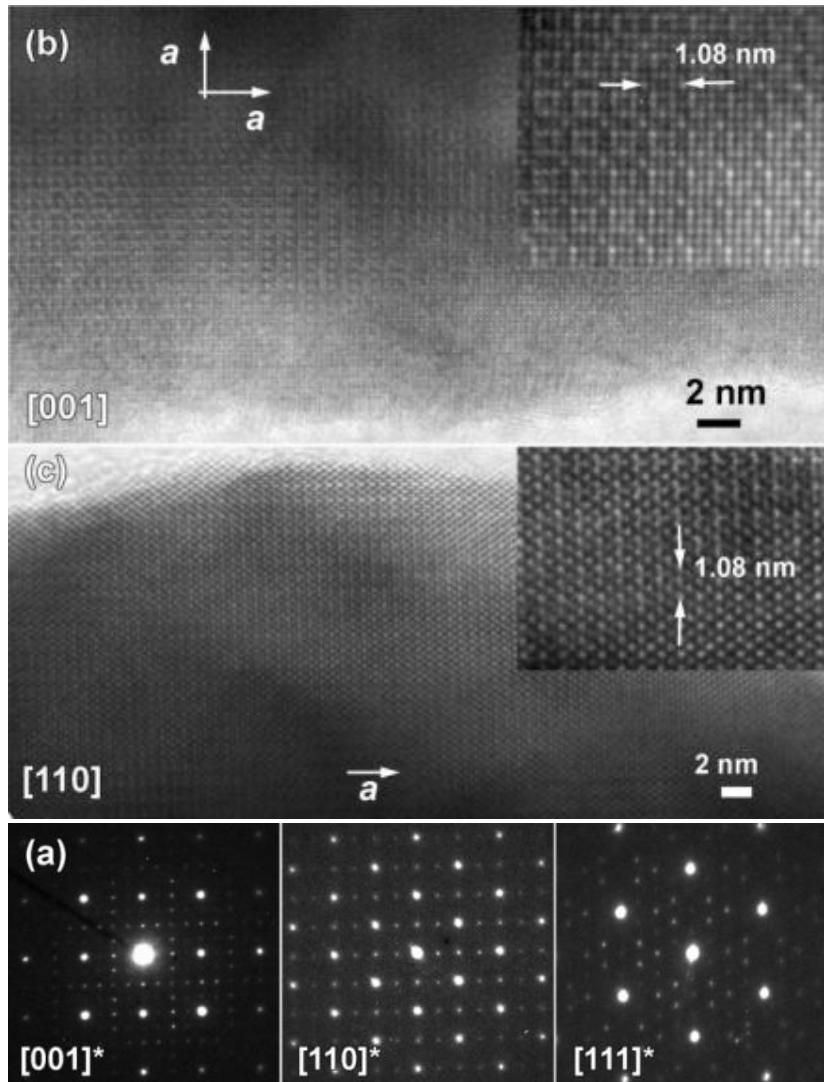


Bulk Cu_{26-x}Zn_xV₂Sn₆S₃₂



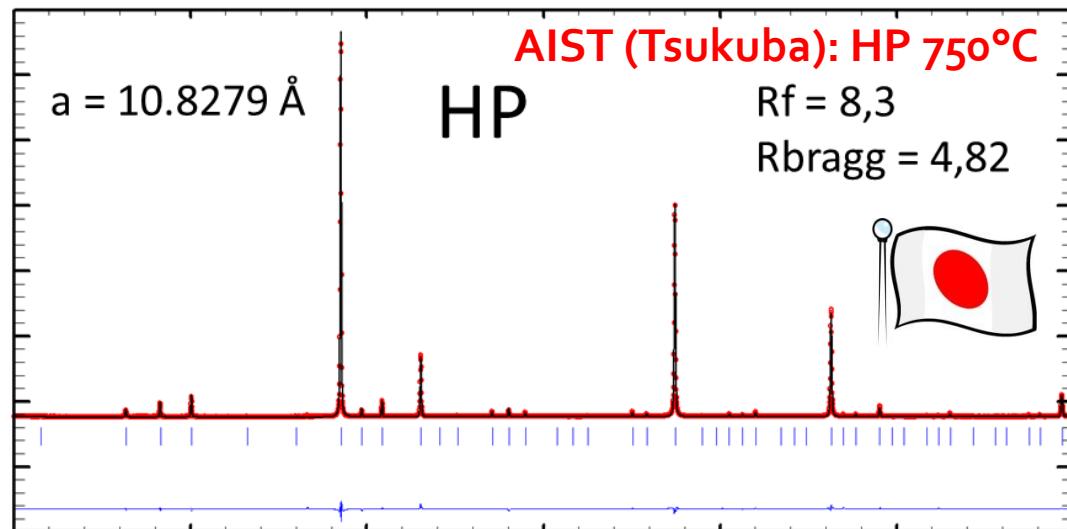
Controlled stoichiometry
Large kappa (metallic behavior)
 $\text{Cu}_{22}^{+}\text{Cu}_4^{2+}\text{V}_2^{5+}\text{Sn}_6^{4+}\text{S}_{32}^{2-}$

Bulk $\text{Cu}_{26-x}\text{Zn}_x\text{V}_2\text{Sn}_6\text{S}_{32}$

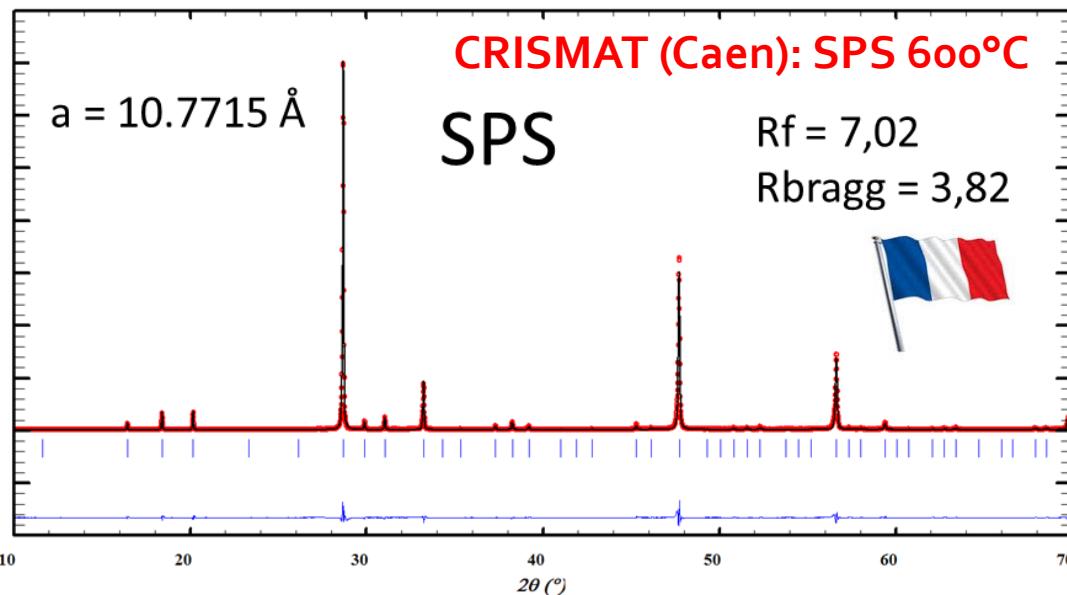


$ZT = 0.4 @ 700\text{K}$ for $x = 1$

French MA Powder densified in Japan & France



High crystallinity & purity.



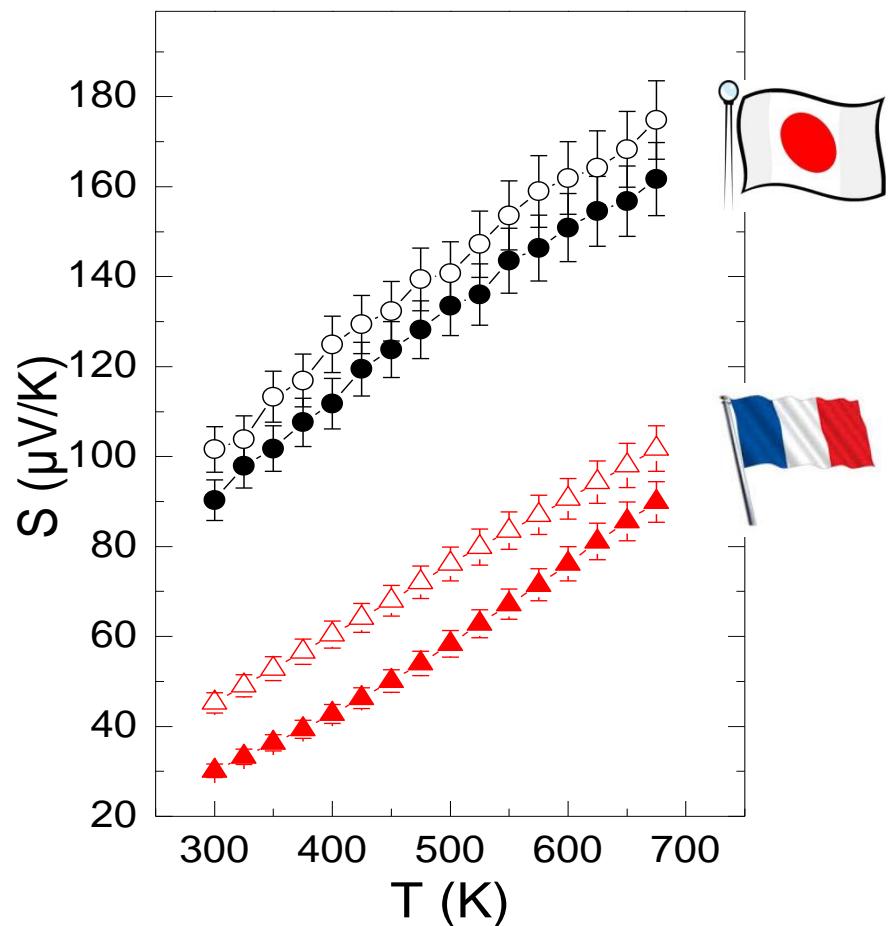
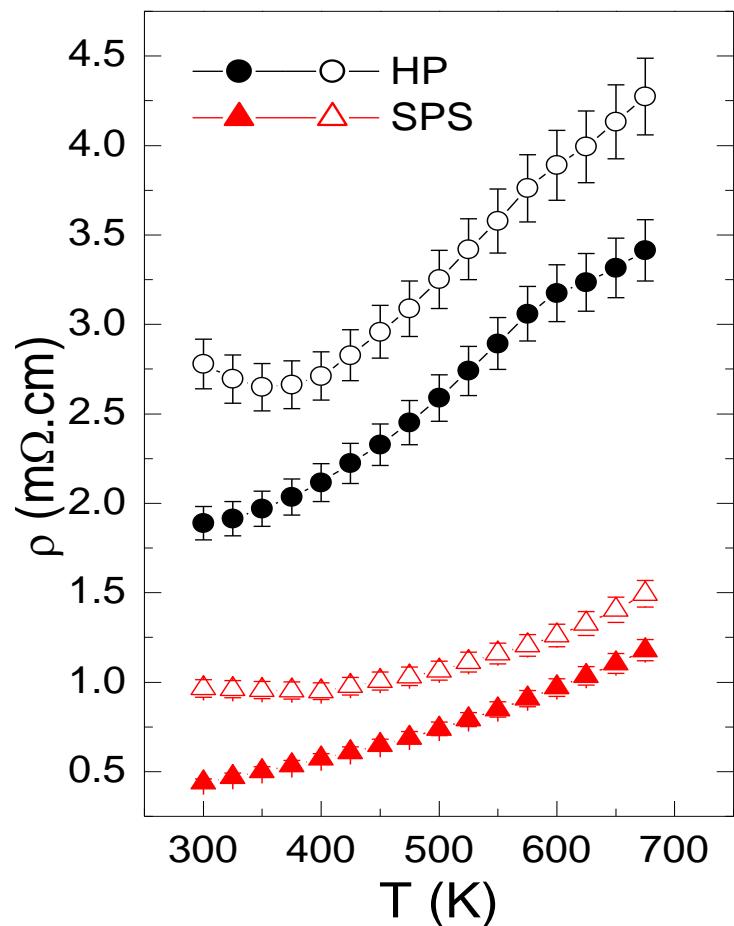
But XRD data and EDS analyses suggest

:

- Sulfur deficiency
- Cu excess

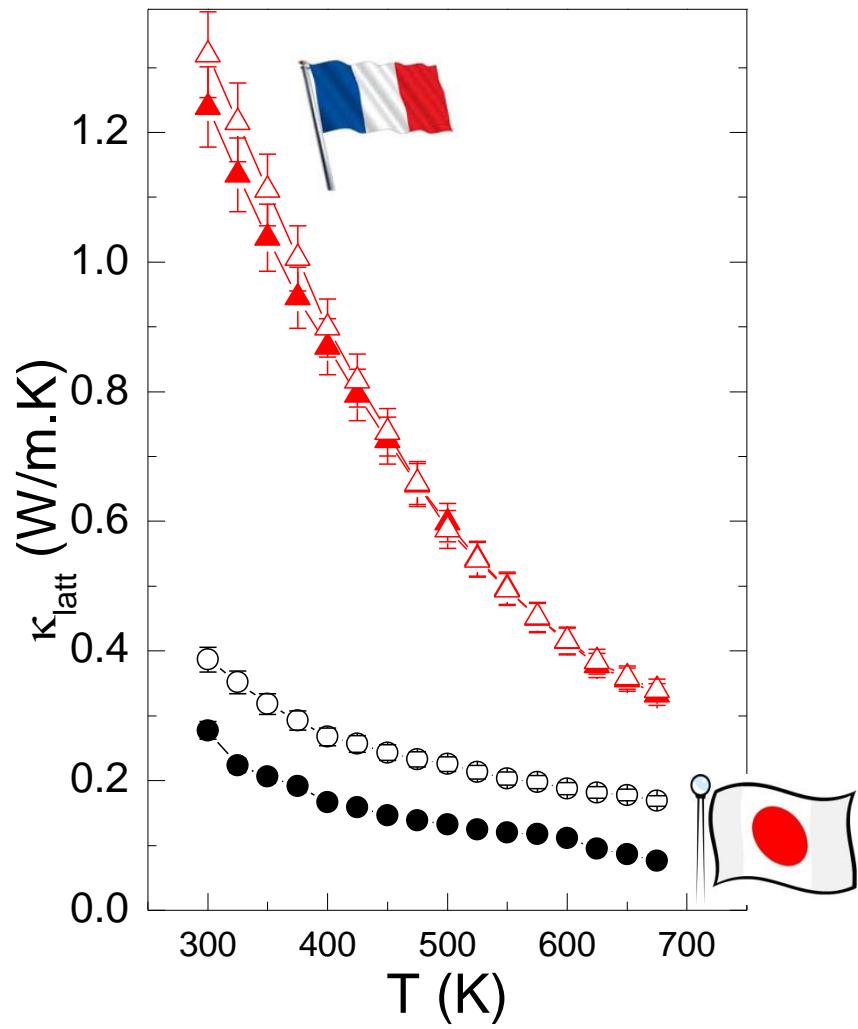
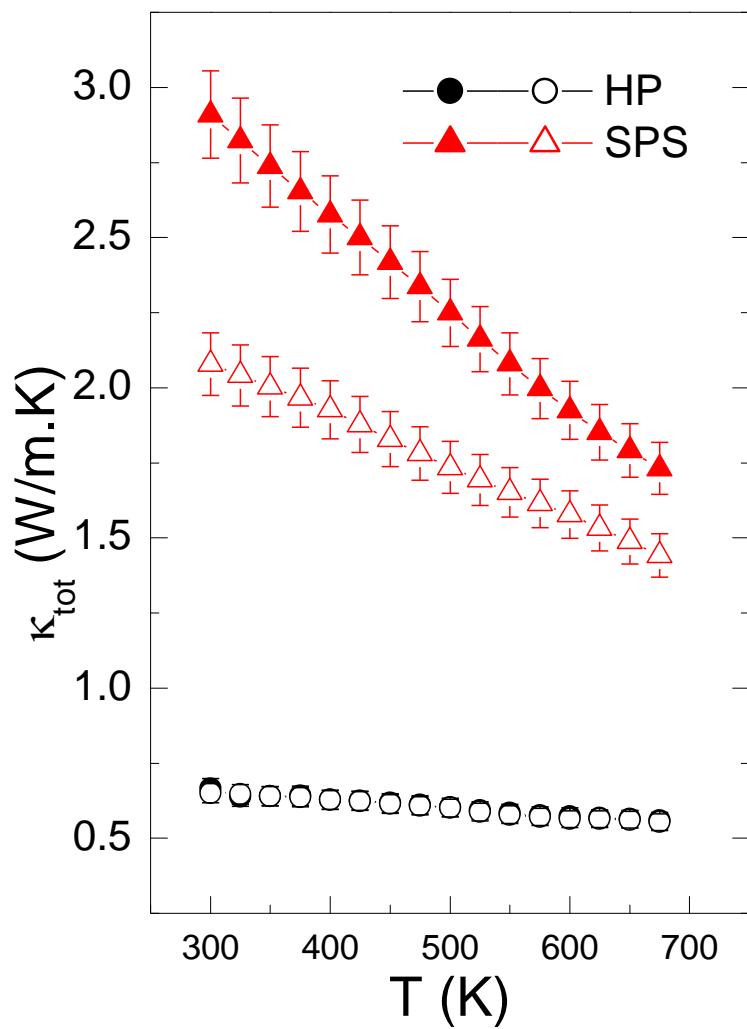
High resolution neutron diffraction is required.

Transport Properties



- Sulfur deficiency → Electron doping in Japanese HP sample.
- Cationic occupancy

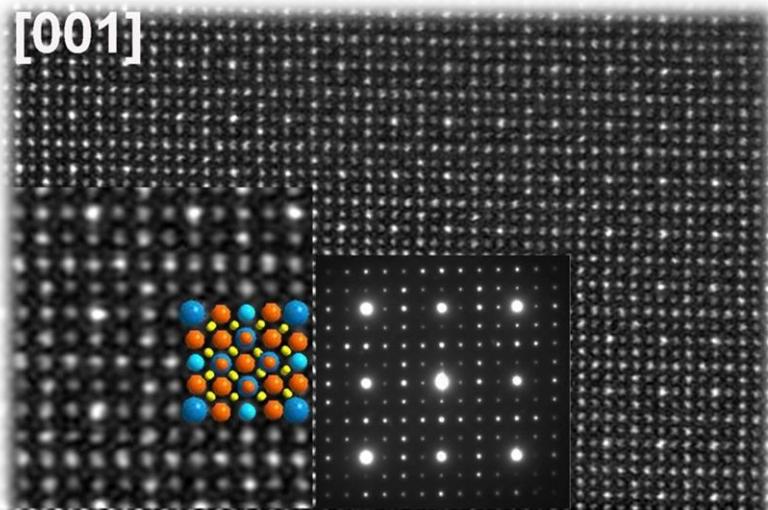
Transport Properties



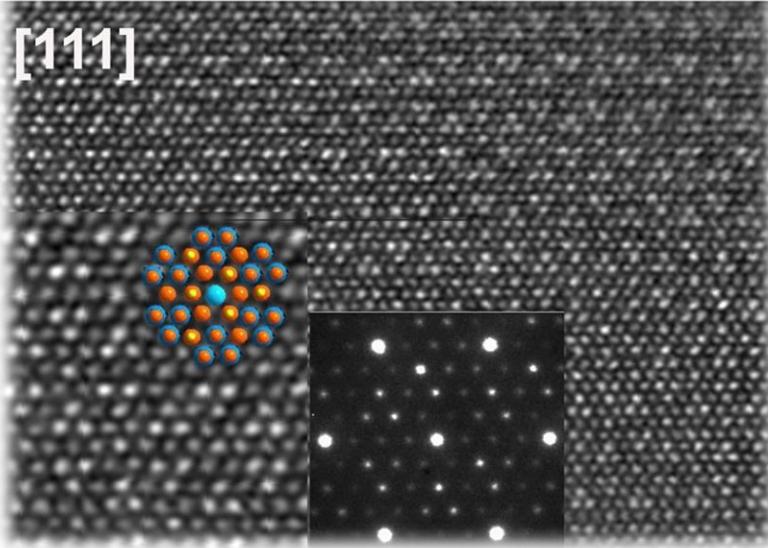
→ Structural/point defects?

French colusite is well ordered!!!!

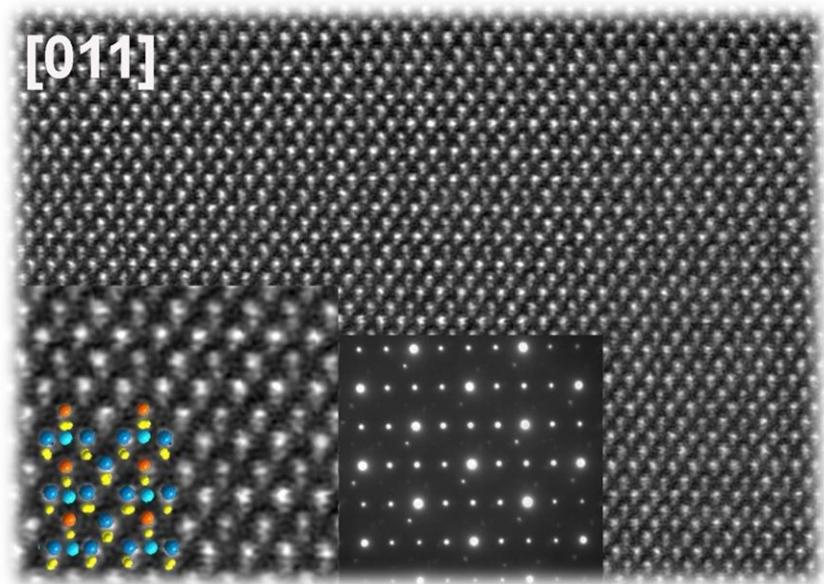
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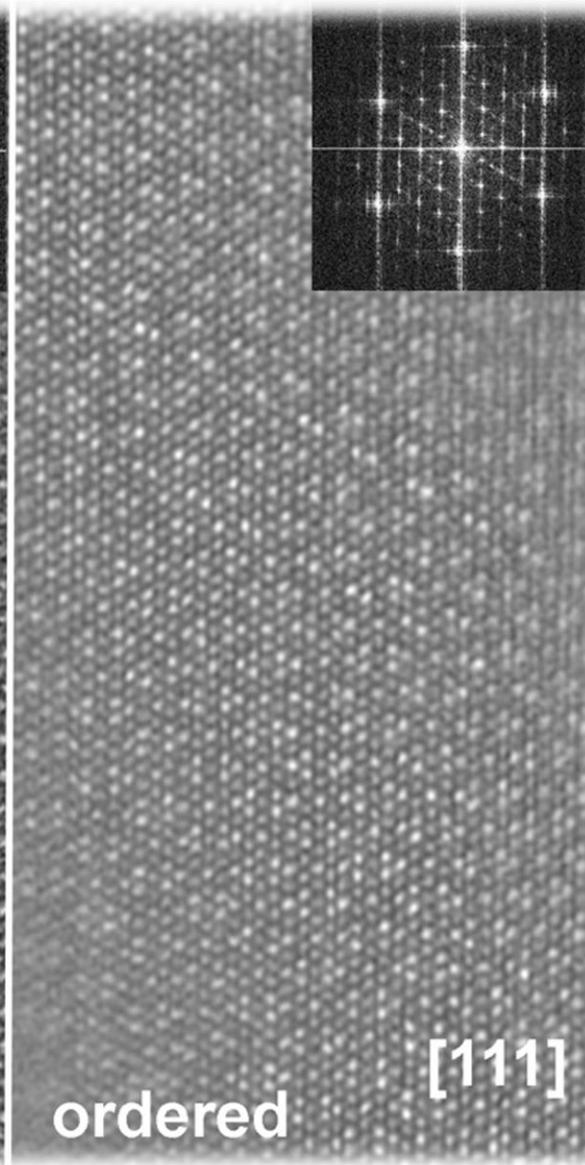
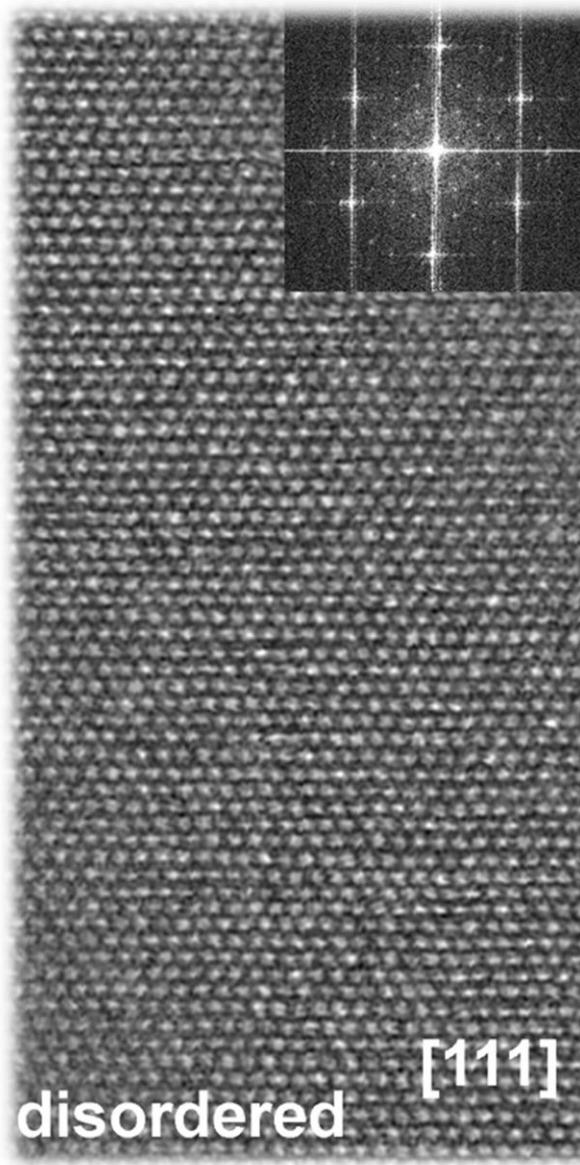
[111]



[011]

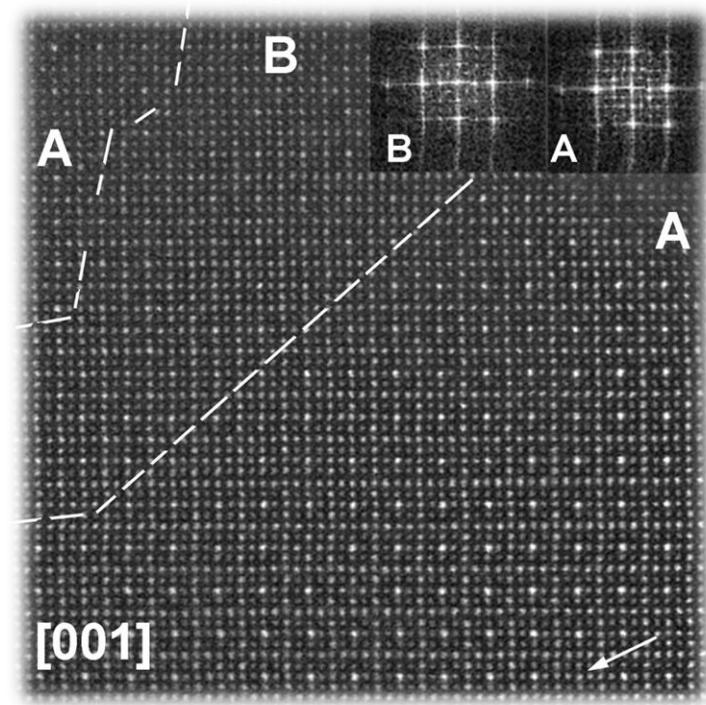
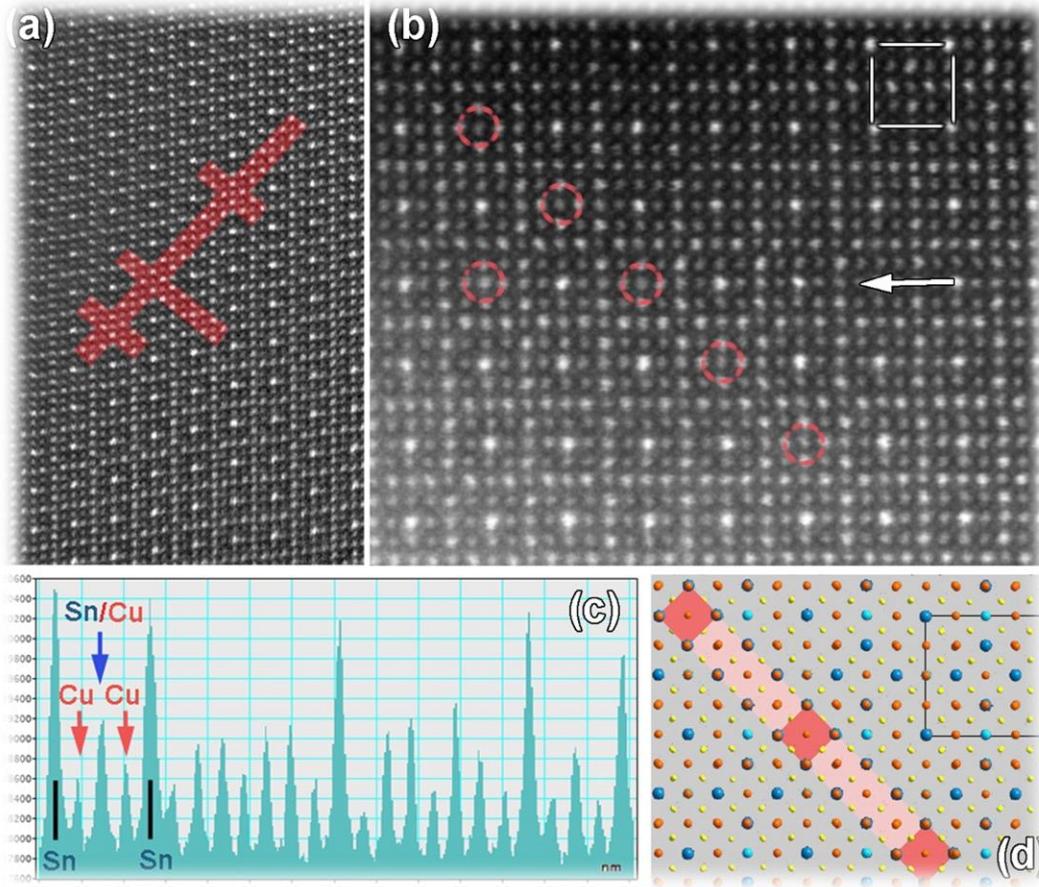


Japanese colusite is disordered

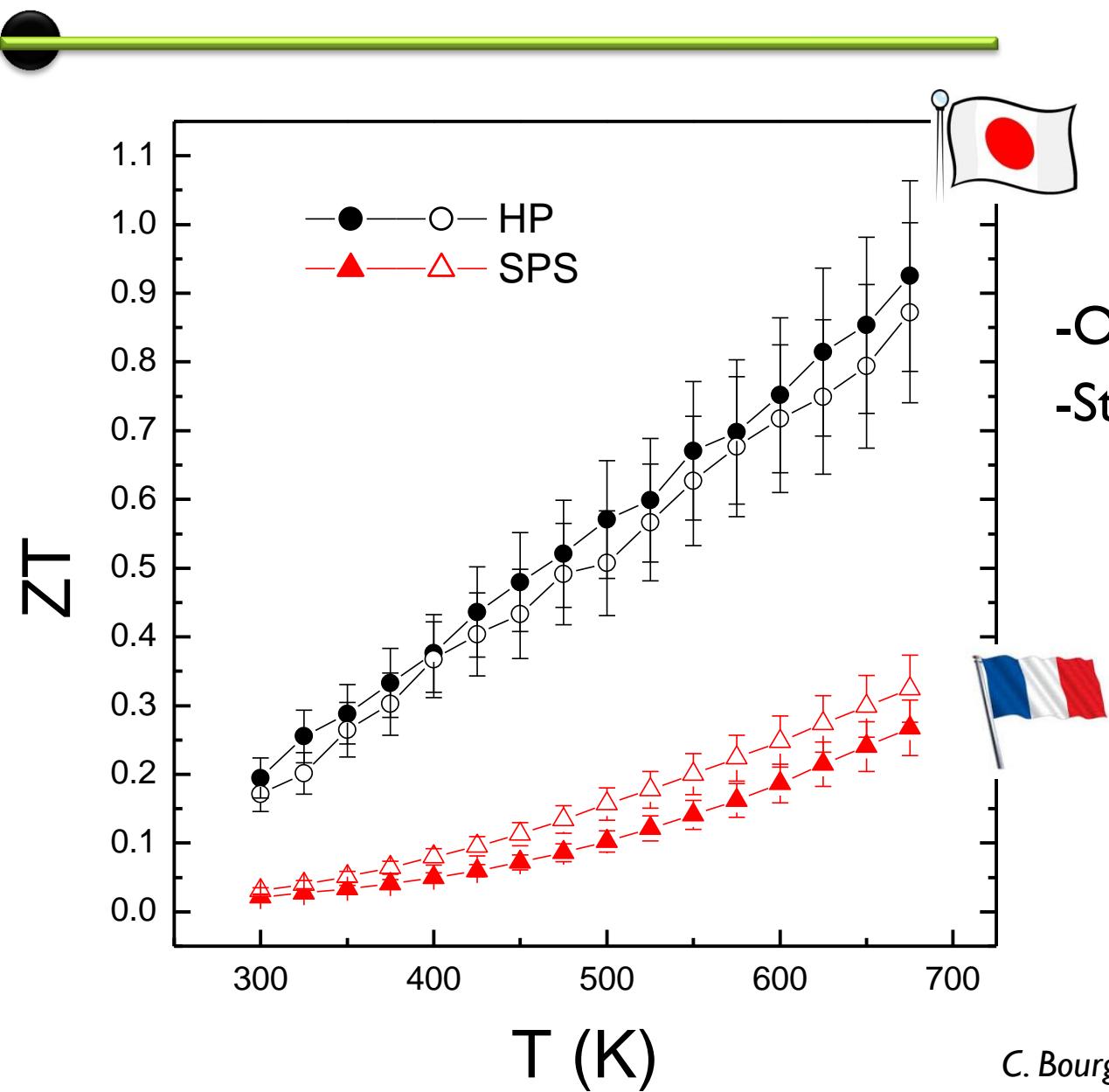


Point defects

→ Cu/Sn mixed occupancy

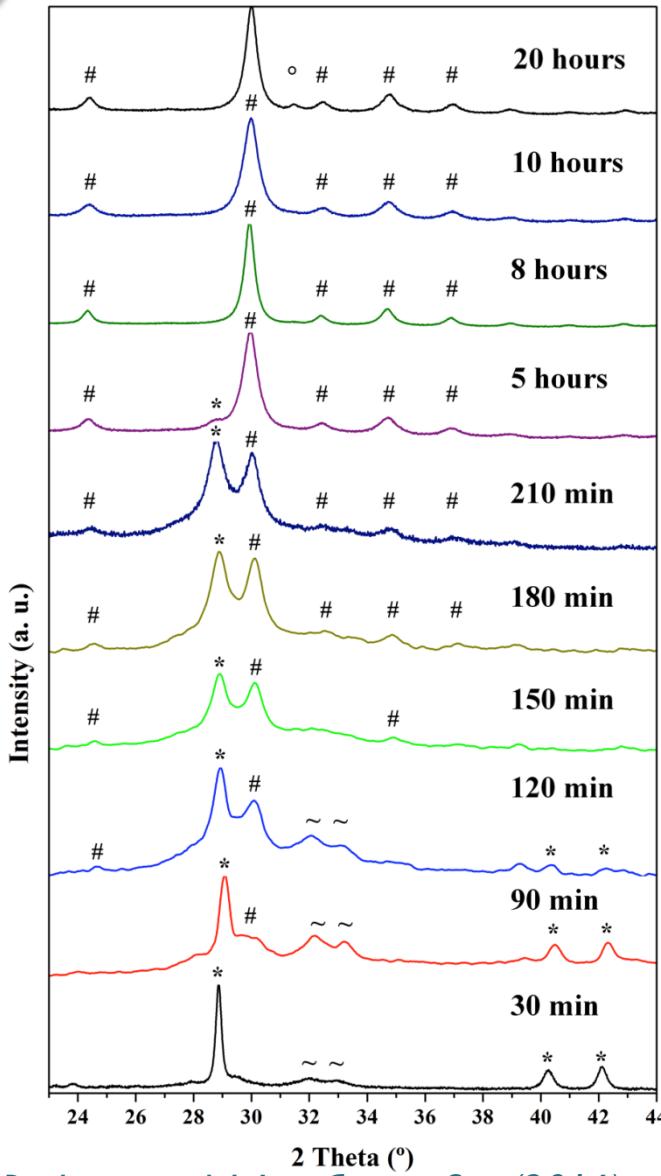


Transport Properties

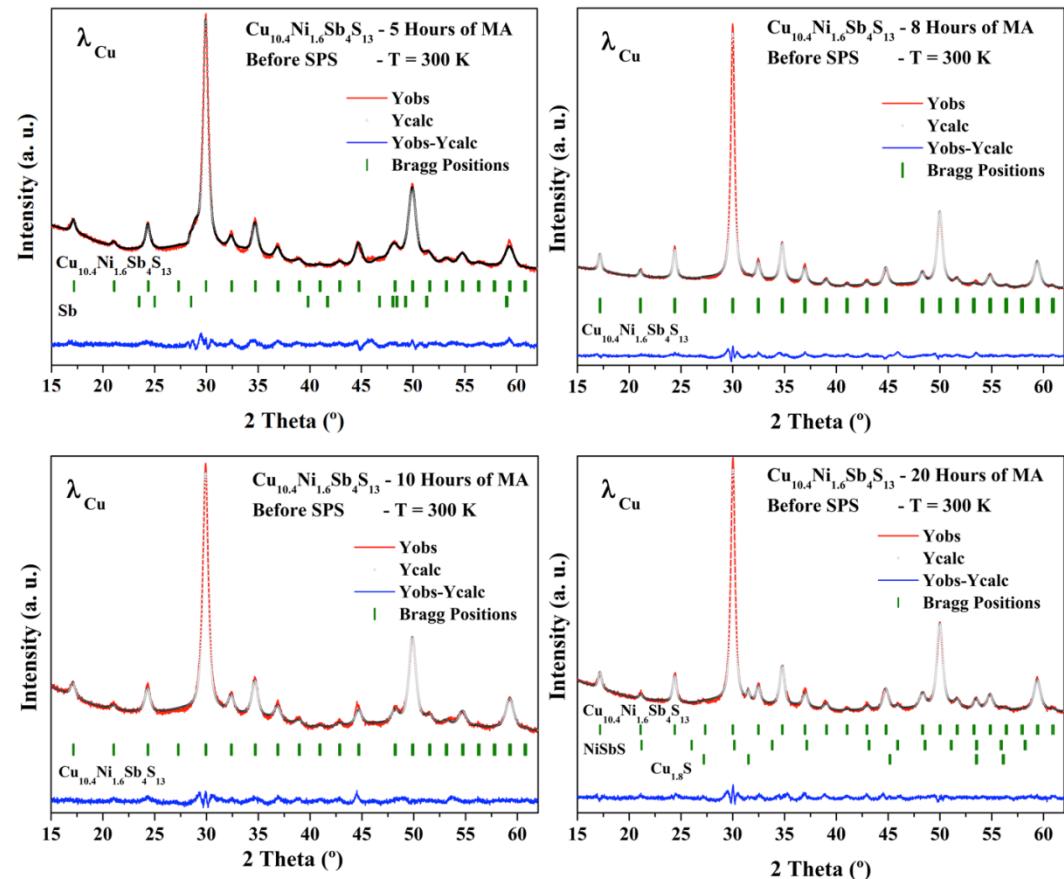


-Optimized carrier conc.
-Structural disordering

Mechanical Alloying of $\text{Cu}_{10.4}\text{Ni}_{1.6}\text{Sb}_4\text{S}_{13}$



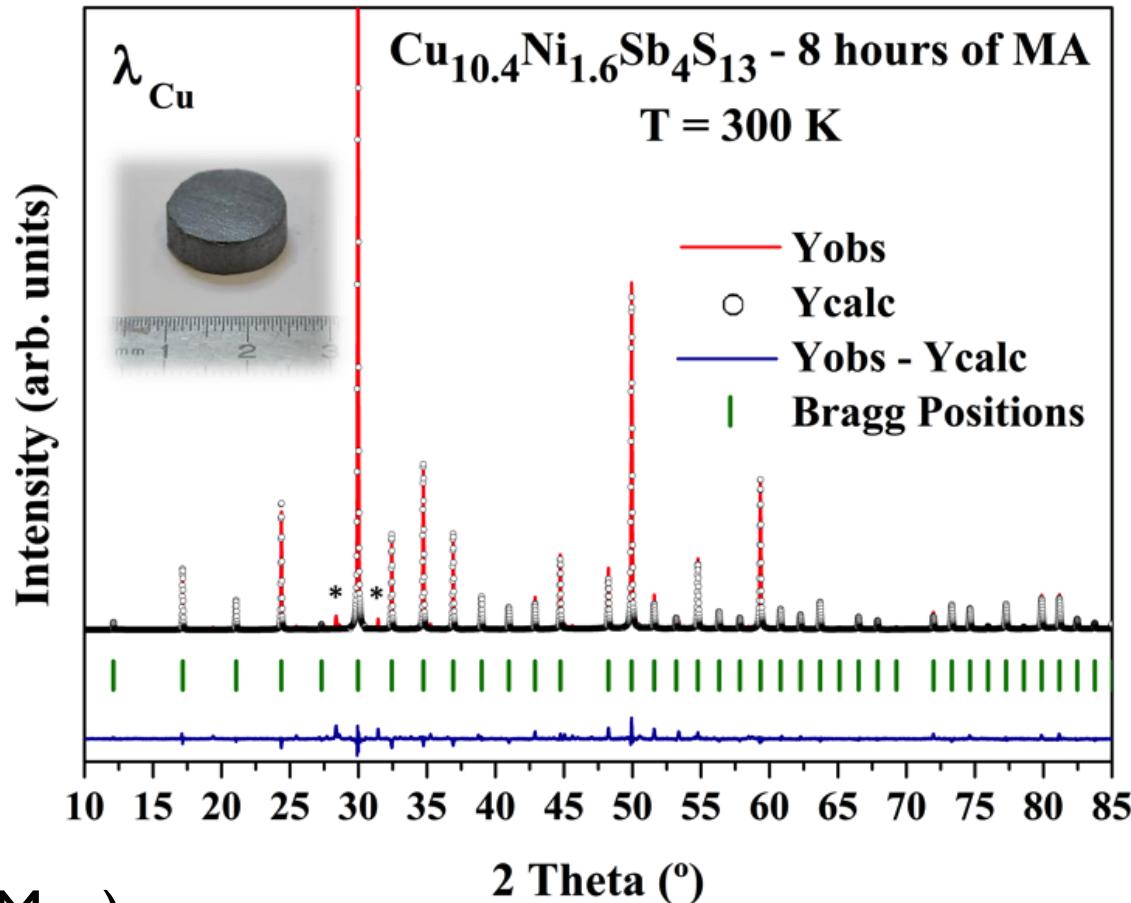
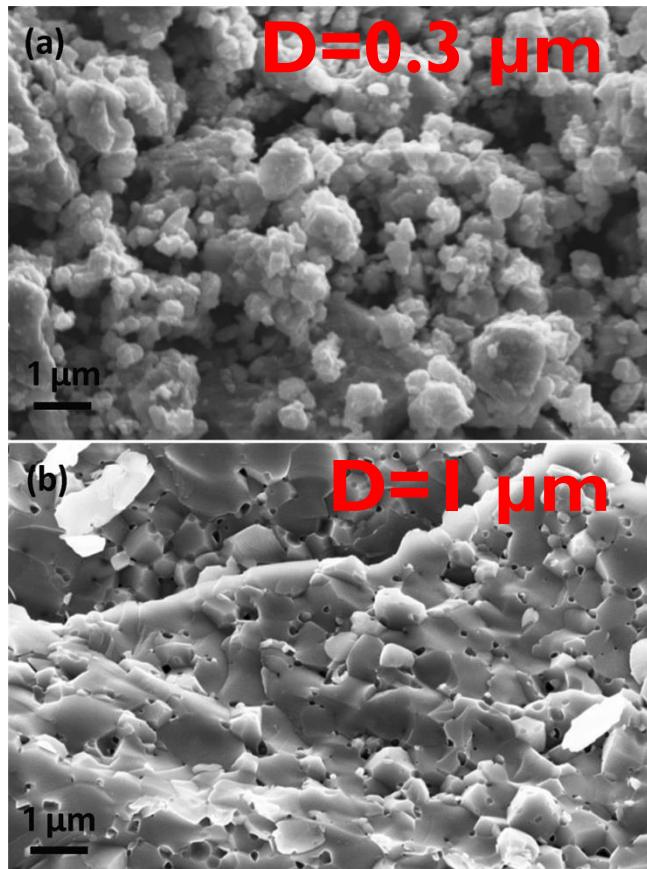
Reaction of stoichiometric mixtures from the elements
WC jars & balls, 600 rpm



Mechanical Alloying of $\text{Cu}_{10.4}\text{Ni}_{1.6}\text{Sb}_4\text{S}_{13}$



As ball-milled

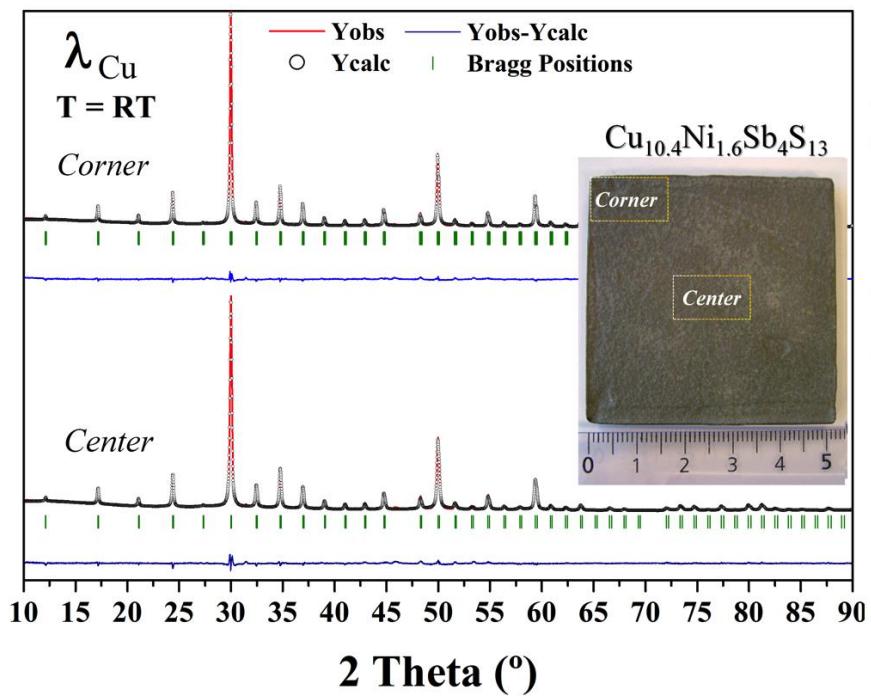


After SPS (480°C/30 min/60 MPa)
density > 95%

Up-scaled SPS Process



Intensity (arb. units)

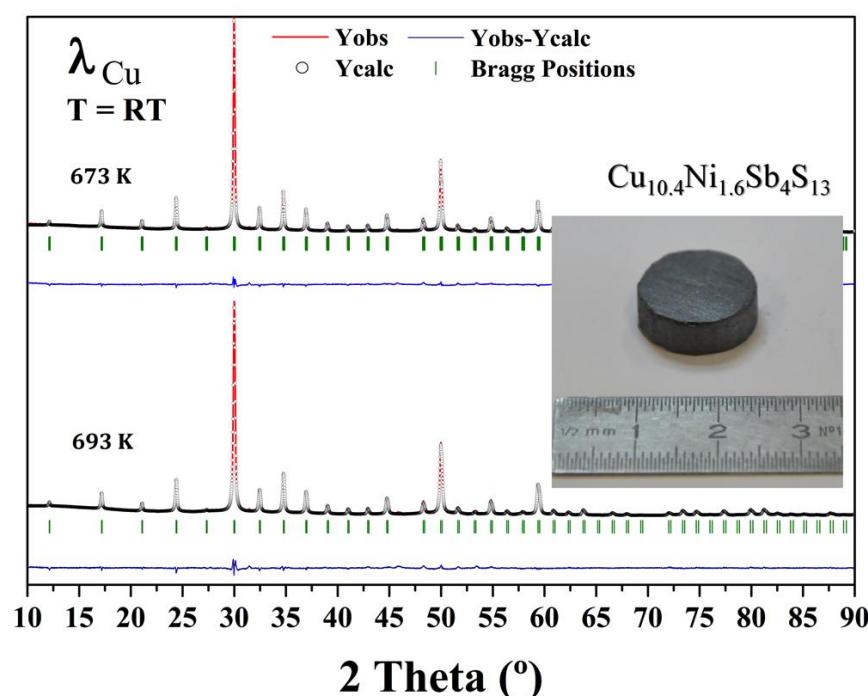


a)

T. Barbier et al. RSC Advances (2016)

T. Barbier et al. J. All. Comp. (2015)

Intensity (arb. units)

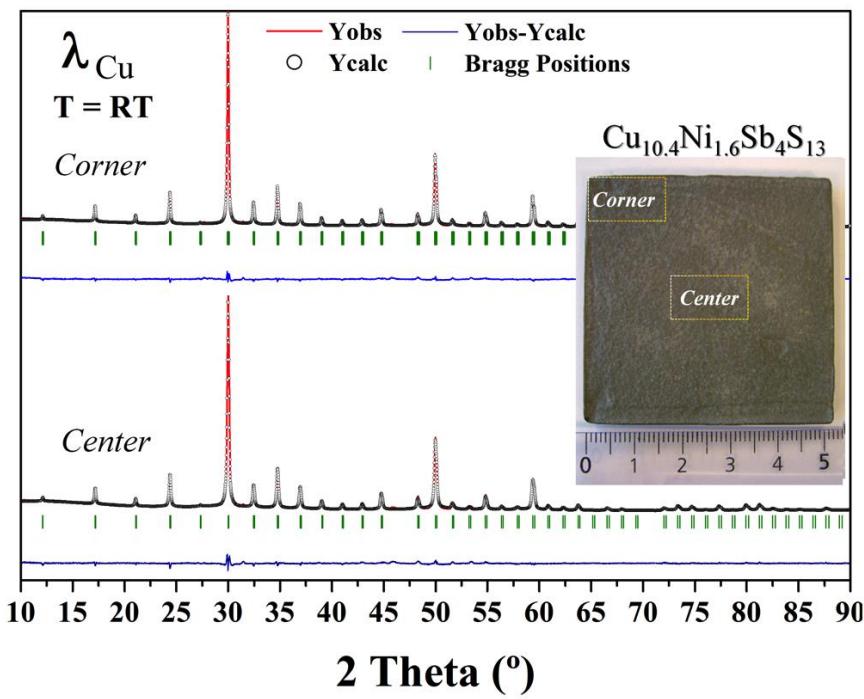


b)

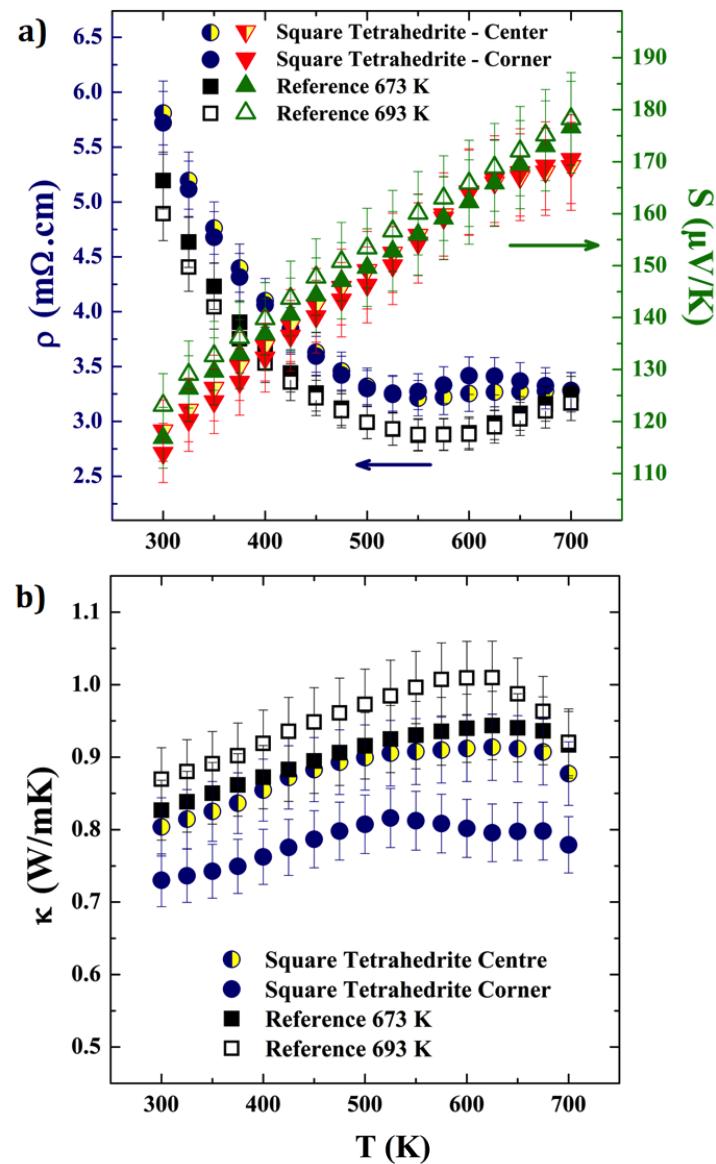
Up-scaled SPS Process



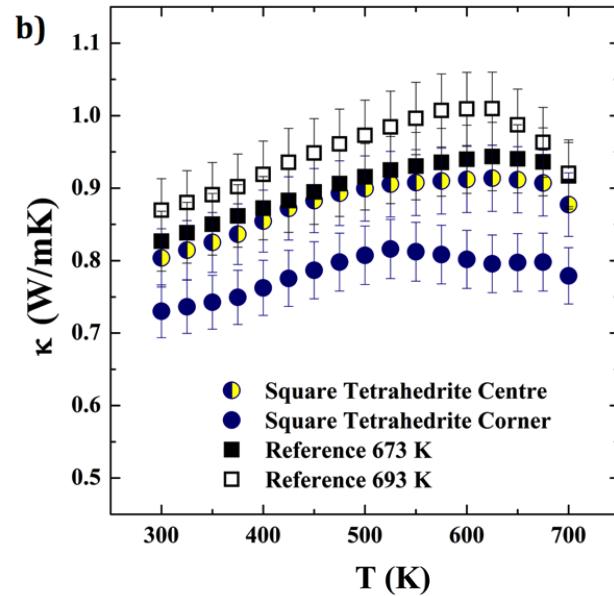
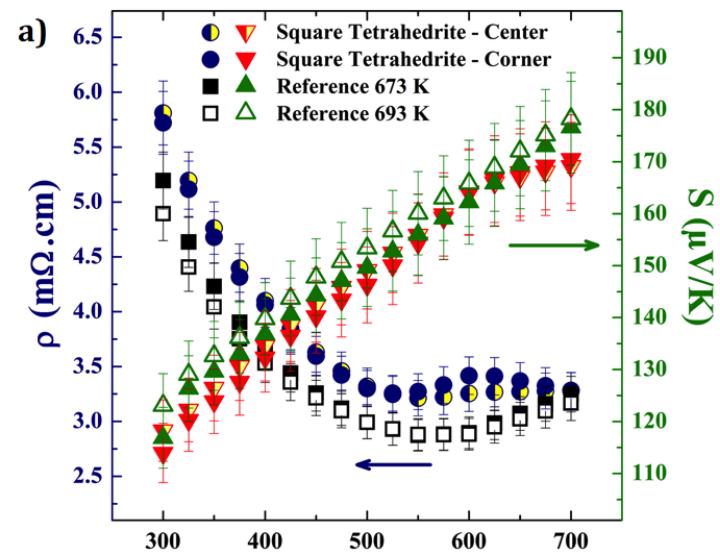
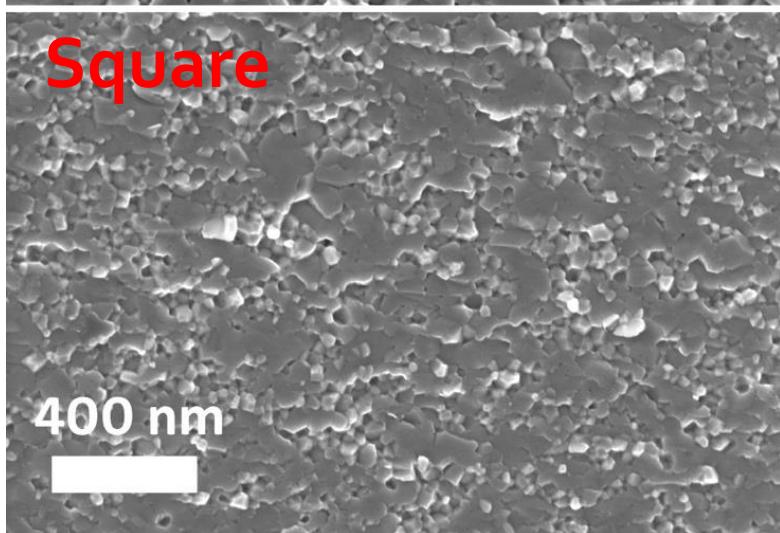
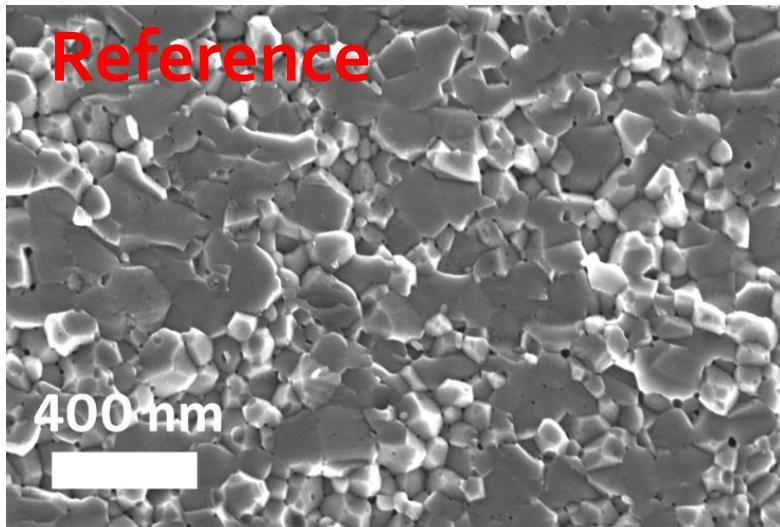
Intensity (arb. units)



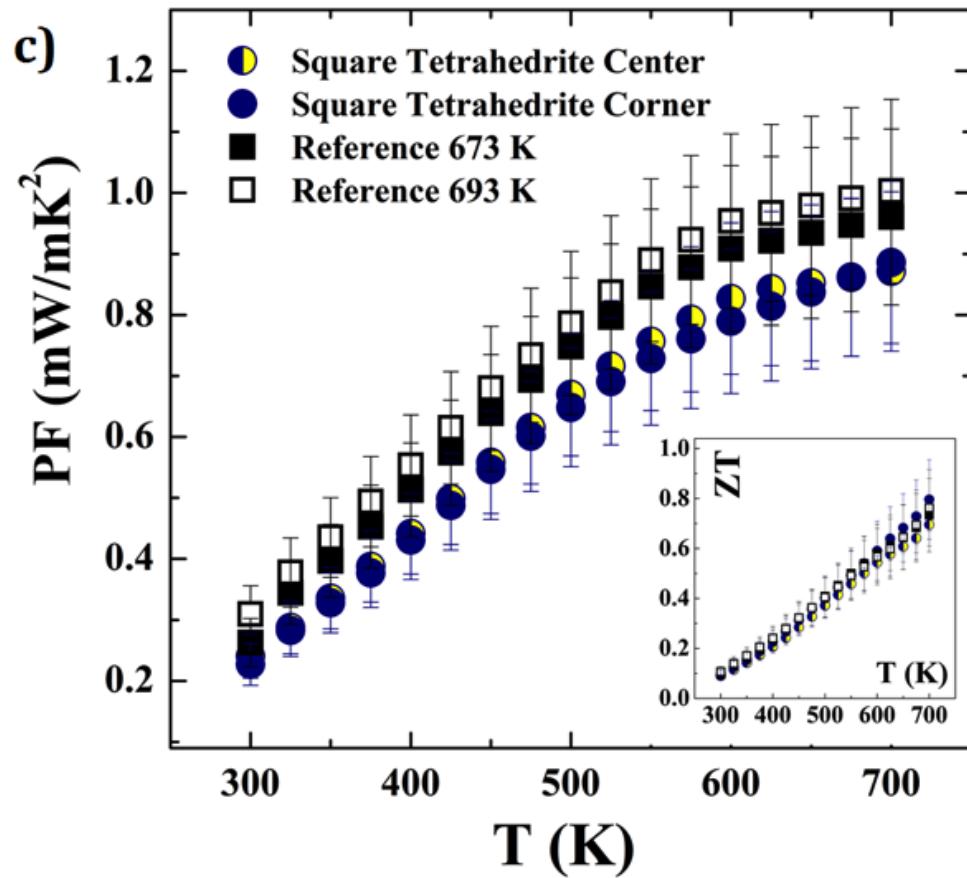
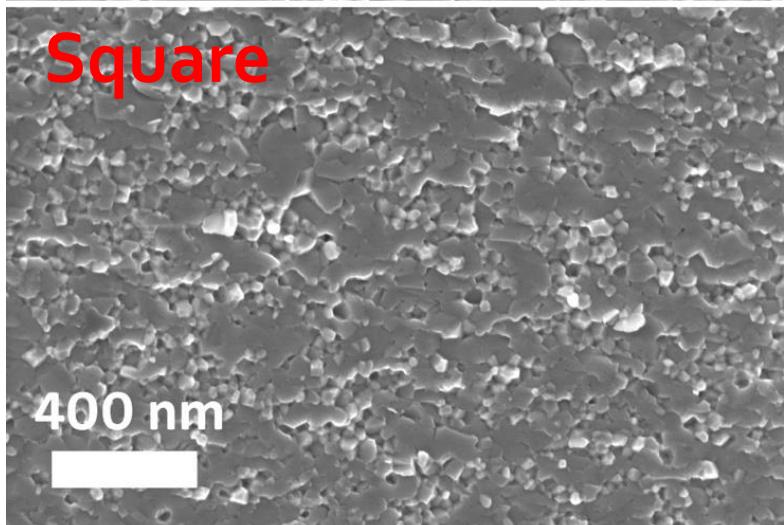
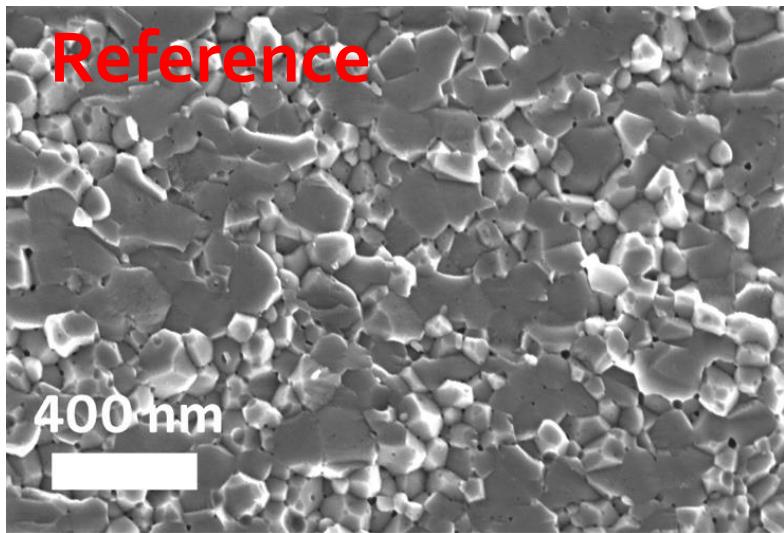
T. Barbier et al. RSC Advances (2016)



Up-scaled SPS Process



Up-scaled SPS Process



Ternary/Quaternary Sulfides

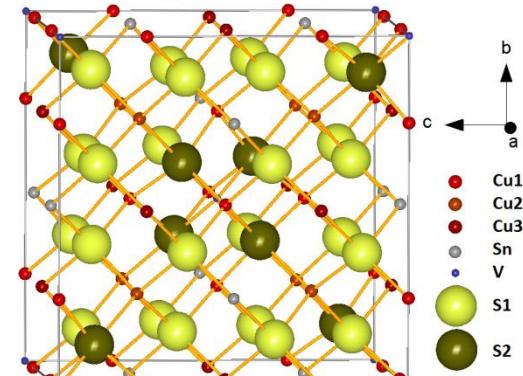
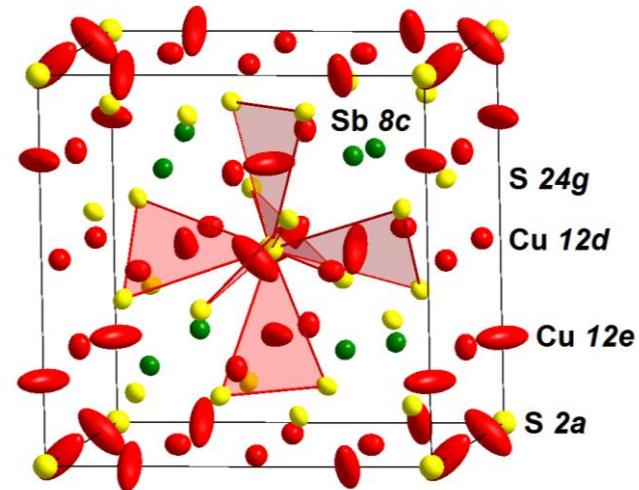
-N-type metallic $\text{Cu}_4\text{Sn}_7\text{S}_{16}$
(ZT=0.2, Acta Mater. 2015)

-Metallic $\text{Cu}_{26}\text{V}_2\text{Sn}_6\text{S}_{32}$ colusite
(ZT=0.4, J. Mater. Chem. C 2016)
(ZT=0.9, soon submitted)

-Metallic $\text{Cu}_{12}\text{Sb}_4\text{S}_{13}$ tetrahedrite
(ZT=0.8, J. All. Comp. 2015, RSC Adv. 2016, JACerS 2016)

-Semicond. $\text{Cu}_8\text{Fe}_3\text{Sn}_2\text{S}_{12}$ Stannoidite
(ZT=0.4, soon submitted)

-Semicond. $\text{Cu}_5\text{FeS}_{4-x}\text{Se}_x$ bornite
(ZT=0.6, Dalton Trans. 2017)



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